



US011996329B2

(12) **United States Patent**
Wang et al.

(10) **Patent No.:** **US 11,996,329 B2**
(45) **Date of Patent:** **May 28, 2024**

(54) **METHOD AND IC DESIGN WITH
NON-LINEAR POWER RAILS**

(56) **References Cited**

(71) Applicant: **Taiwan Semiconductor
Manufacturing Co., Ltd.**, Hsin-Chu
(TW)

U.S. PATENT DOCUMENTS

6,226,560 B1 5/2001 Hama et al.
7,557,436 B2 7/2009 Mizuno et al.
(Continued)

(72) Inventors: **Sheng-Hsiung Wang**, Hsinchu County
(TW); **Bao-Ru Young**, Hsinchu County
(TW); **Tung-Heng Hsieh**, Hsinchu
County (TW)

FOREIGN PATENT DOCUMENTS

CN 105390538 A 3/2016
CN 105514083 A 4/2016
(Continued)

(73) Assignee: **TAIWAN SEMICONDUCTOR
MANUFACTURING CO., LTD.**,
Hsinchu (TW)

OTHER PUBLICATIONS

(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

W. Maly, "Technology of the SRAM", Atlas of IC Technologies: An
Introduction to VLSI Processes, 1987, pp. 295-301, The Benjamin/
Cummings Publishing Company, Inc., Electrical and Computer
Engineering Department, Carnegie-Mellon University.

(21) Appl. No.: **18/162,841**

Primary Examiner — Tu-Tu V Ho

(22) Filed: **Feb. 1, 2023**

(74) *Attorney, Agent, or Firm* — Haynes and Boone, LLP

(65) **Prior Publication Data**

US 2023/0187277 A1 Jun. 15, 2023

Related U.S. Application Data

(60) Continuation of application No. 17/106,639, filed on
Nov. 30, 2020, now Pat. No. 11,581,221, which is a
(Continued)

(57) **ABSTRACT**

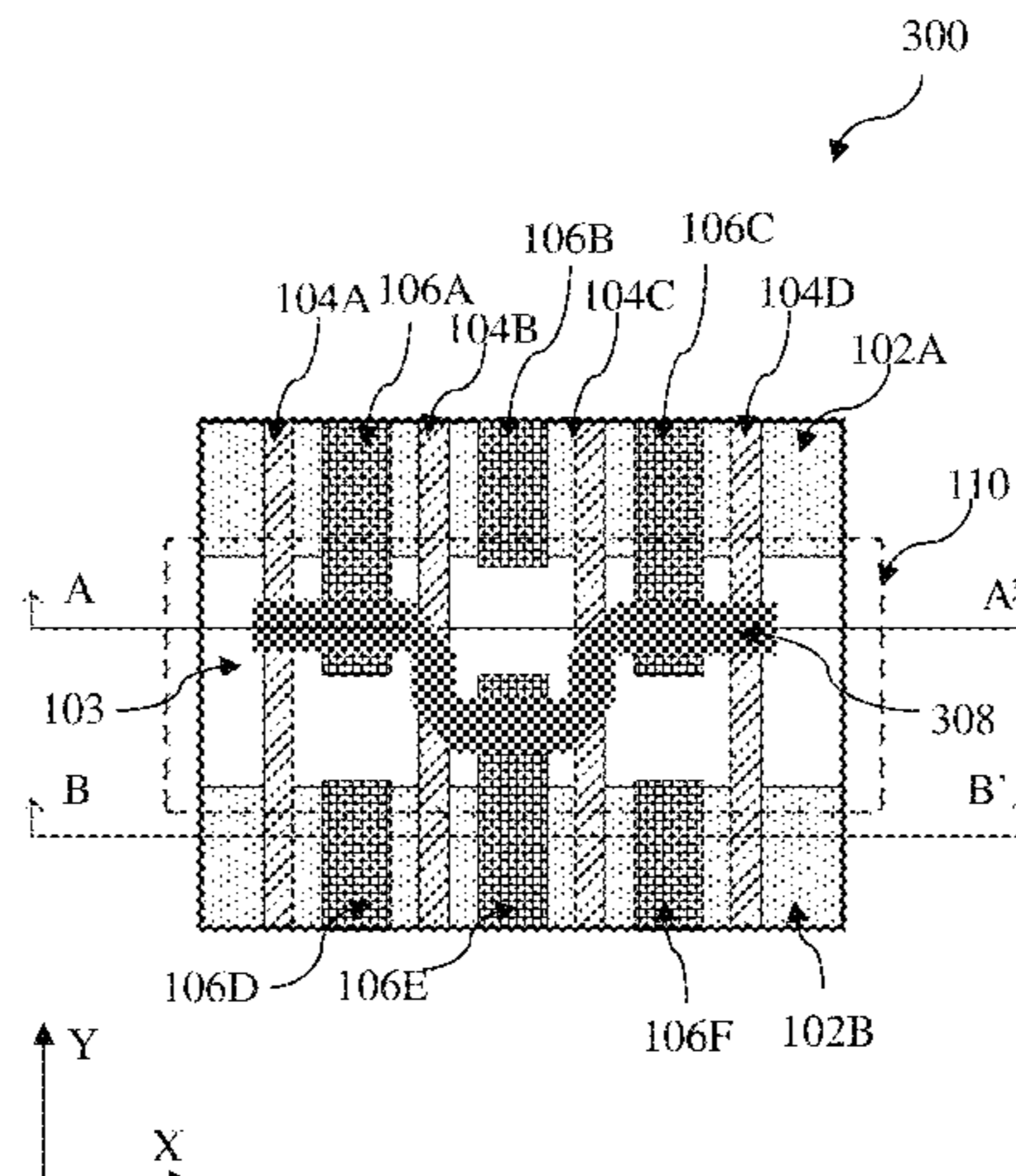
The present disclosure provides a method for fabricating an
integrated circuit (IC). The method includes receiving an IC
layout having a first pattern layer that includes first source/
drain (S/D) contacts and second S/D contacts, the first and
second S/D contacts are spaced away from each other by a
spacing along a first direction, and each of the first and
second S/D contacts have elongated shapes extending
lengthwise in a second direction perpendicular to the first
direction. The method includes constructing a conductive
feature on a second pattern layer of the IC layout, the
conductive feature having an initial rectangular shape with
a length and a width, the length extending along the first
direction. And the method includes modifying the conductive
feature to form a modified conductive feature that is
overlapped with the first S/D contacts and distanced away
from the second S/D contacts.

(51) **Int. Cl.**
H01L 21/768 (2006.01)
G06F 30/39 (2020.01)
(Continued)

(52) **U.S. Cl.**
CPC **H01L 21/76892** (2013.01); **G06F 30/39**
(2020.01); **G06F 30/398** (2020.01);
(Continued)

(58) **Field of Classification Search**
CPC H01L 21/76892; H01L 21/76895; H01L
22/20; H01L 23/50; H01L 23/5226;
(Continued)

20 Claims, 11 Drawing Sheets



Related U.S. Application Data

continuation of application No. 16/725,013, filed on Dec. 23, 2019, now Pat. No. 10,854,512, which is a division of application No. 15/686,336, filed on Aug. 25, 2017, now Pat. No. 10,515,850.

- (51) **Int. Cl.**
G06F 30/398 (2020.01)
H01L 21/66 (2006.01)
H01L 23/50 (2006.01)
H01L 23/522 (2006.01)
H01L 23/528 (2006.01)
H01L 27/02 (2006.01)
G06F 119/18 (2020.01)
H01L 27/118 (2006.01)

- (52) **U.S. Cl.**
 CPC *H01L 21/76895* (2013.01); *H01L 22/20* (2013.01); *H01L 23/50* (2013.01); *H01L 23/5226* (2013.01); *H01L 23/5283* (2013.01); *H01L 23/5286* (2013.01); *H01L 27/0207* (2013.01); *G06F 2119/18* (2020.01); *H01L 2027/11881* (2013.01)

- (58) **Field of Classification Search**
 CPC H01L 23/5283; H01L 23/5286; H01L 27/0207; H01L 2027/11881; G06F 30/398; G06F 30/39; G06F 2119/18
 USPC 438/6
 See application file for complete search history.

(56)

References Cited

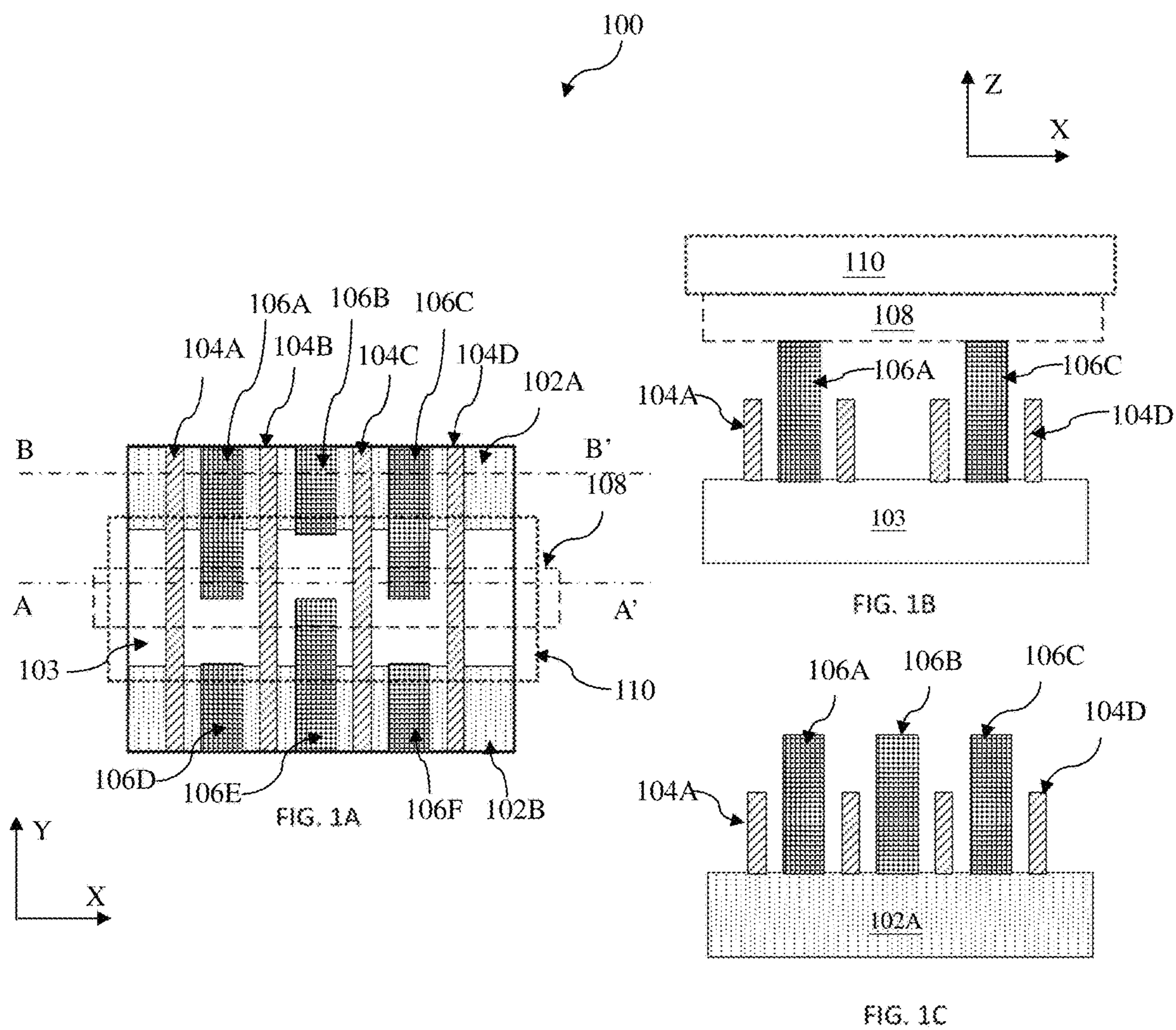
U.S. PATENT DOCUMENTS

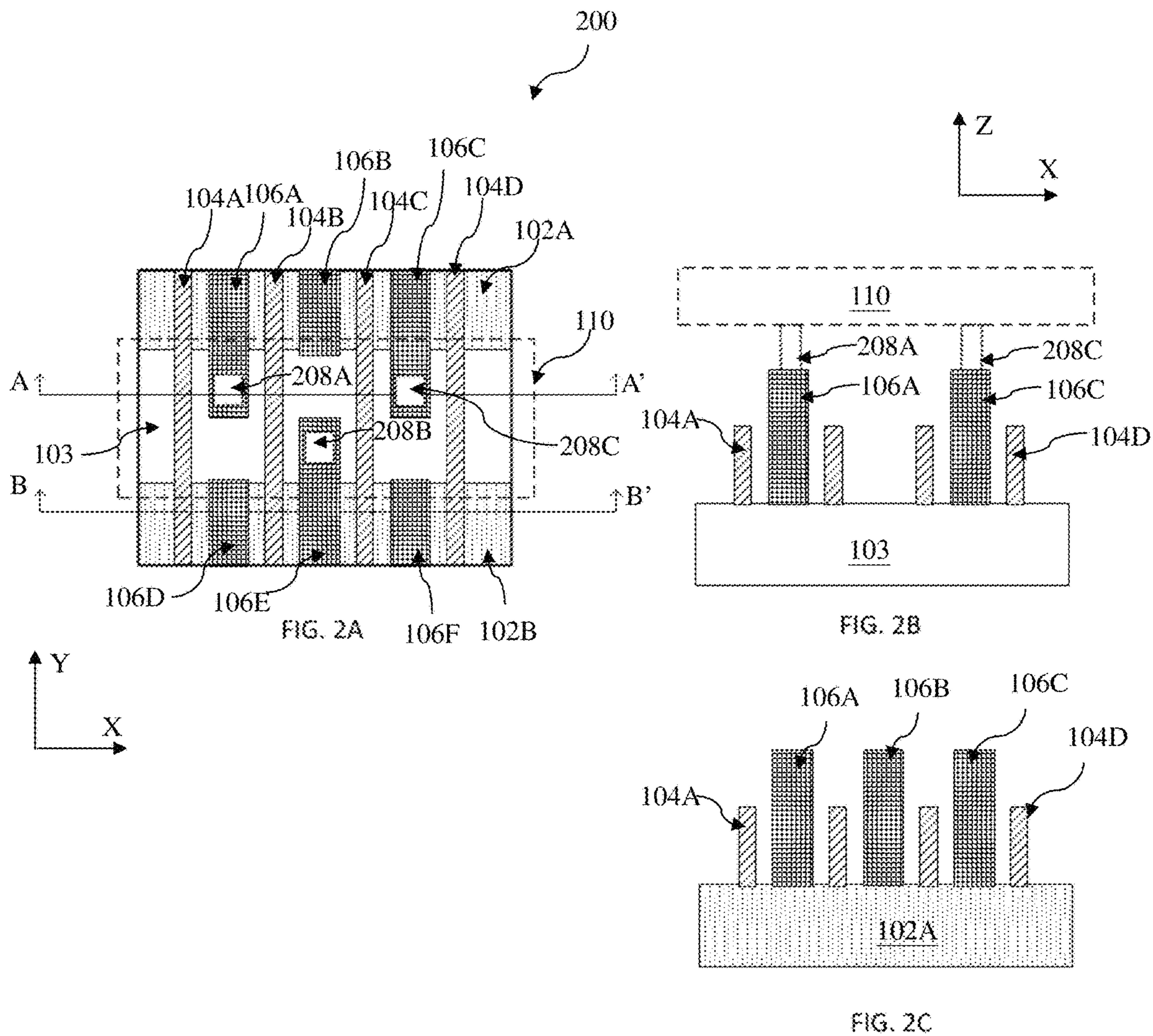
8,772,109	B2	7/2014	Colinge	
8,785,285	B2	7/2014	Tsai et al.	
8,816,444	B2	8/2014	Wann et al.	
8,823,065	B2	9/2014	Wang et al.	
8,860,148	B2	10/2014	Hu et al.	
9,105,490	B2	8/2015	Wang et al.	
9,236,267	B2	1/2016	De et al.	
9,236,300	B2	1/2016	Liaw	
9,520,482	B1	12/2016	Chang et al.	
9,576,814	B2	2/2017	Wu et al.	
9,679,977	B2*	6/2017	Kim	H01L 21/823871
10,515,850	B2	12/2019	Wang et al.	
10,854,512	B2	12/2020	Wang et al.	
2003/0162103	A1	8/2003	Oshima et al.	
2007/0049010	A1	3/2007	Burgess et al.	
2010/0044757	A1	2/2010	Maekawa	
2013/0095650	A1	4/2013	Shimomura	
2013/0280905	A1	10/2013	Doman et al.	
2015/0194427	A1	7/2015	Sengupta et al.	
2015/0294056	A1	10/2015	Lin et al.	
2015/0294057	A1	10/2015	Lin et al.	
2016/0093603	A1	3/2016	Hsieh et al.	

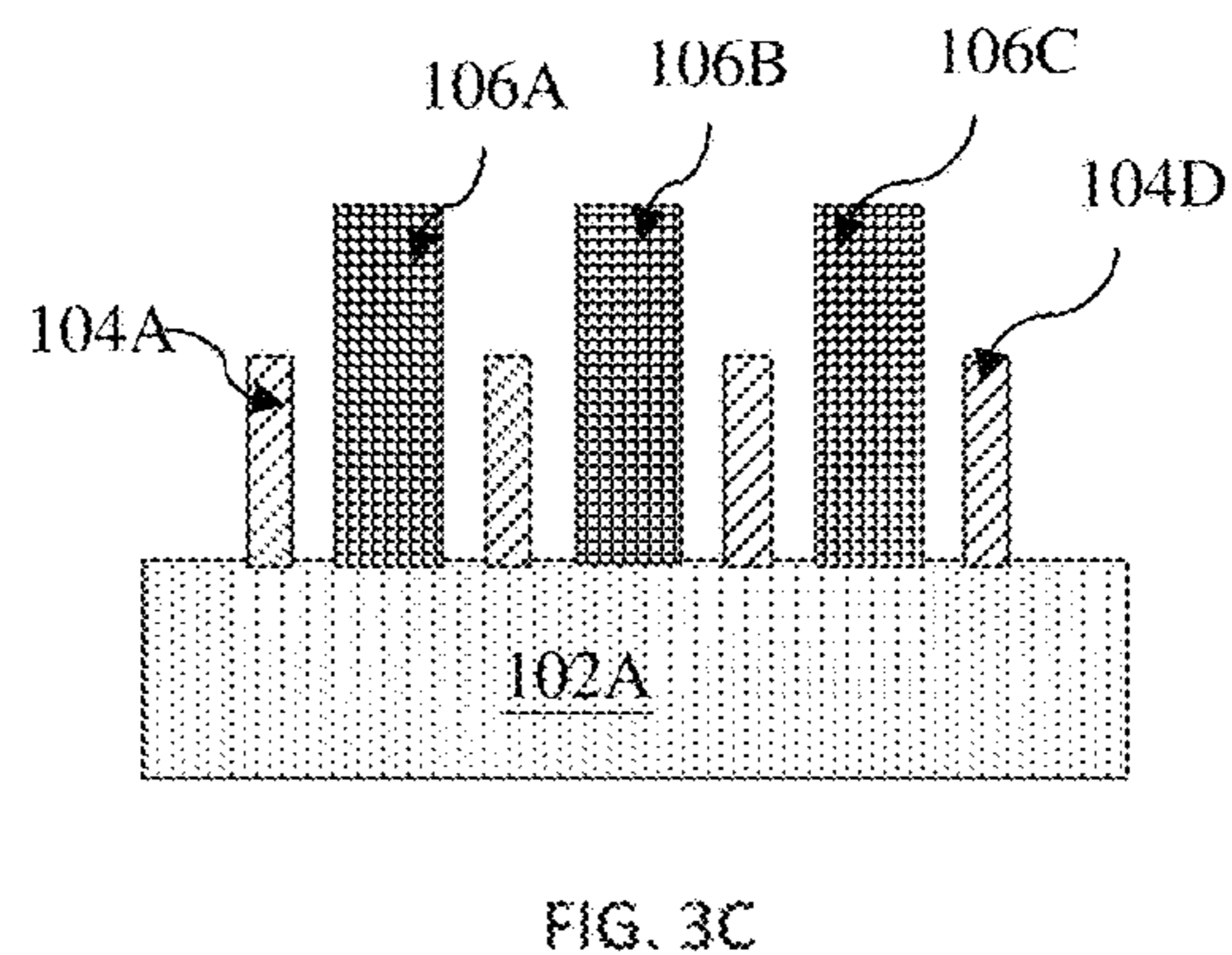
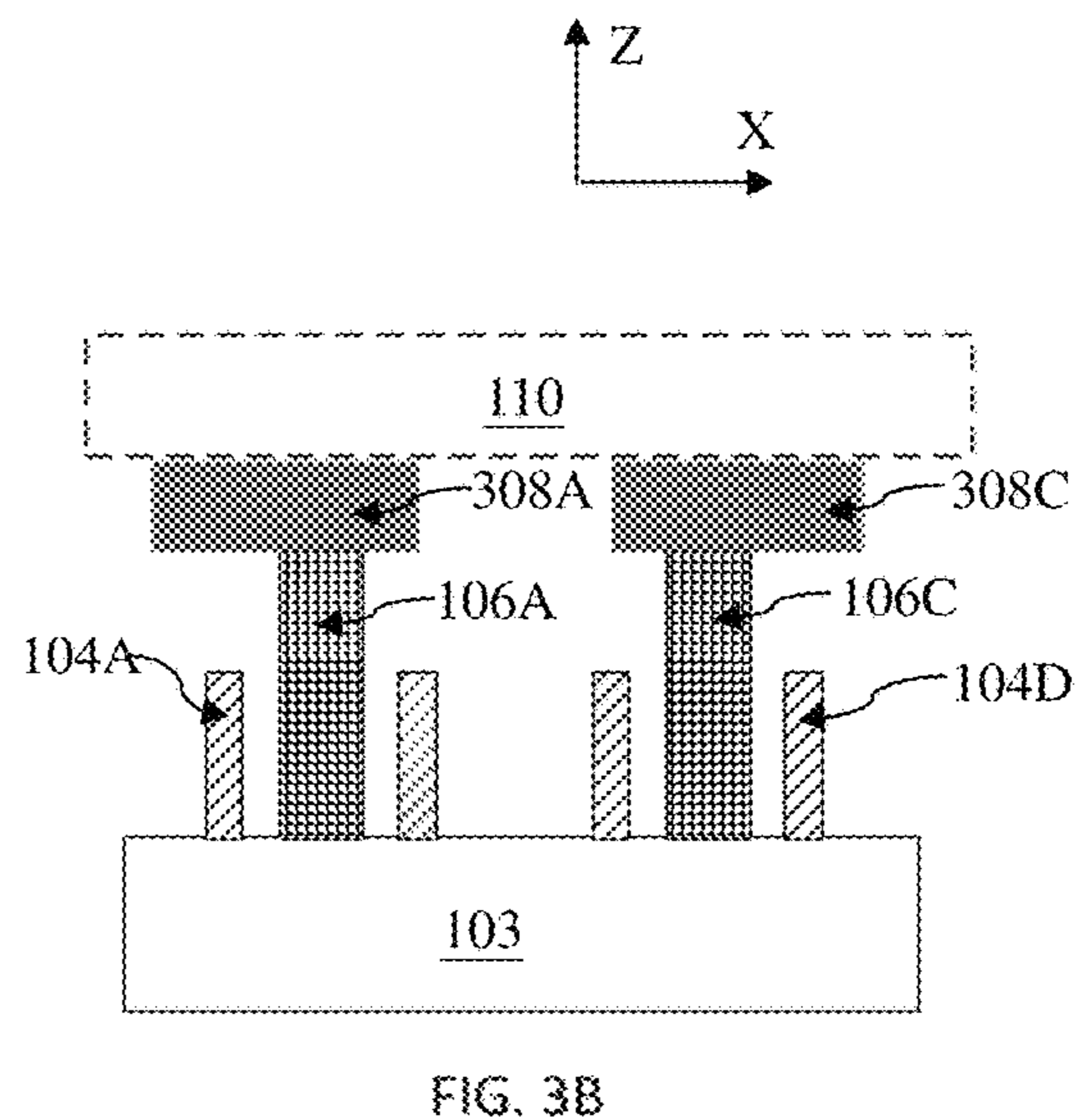
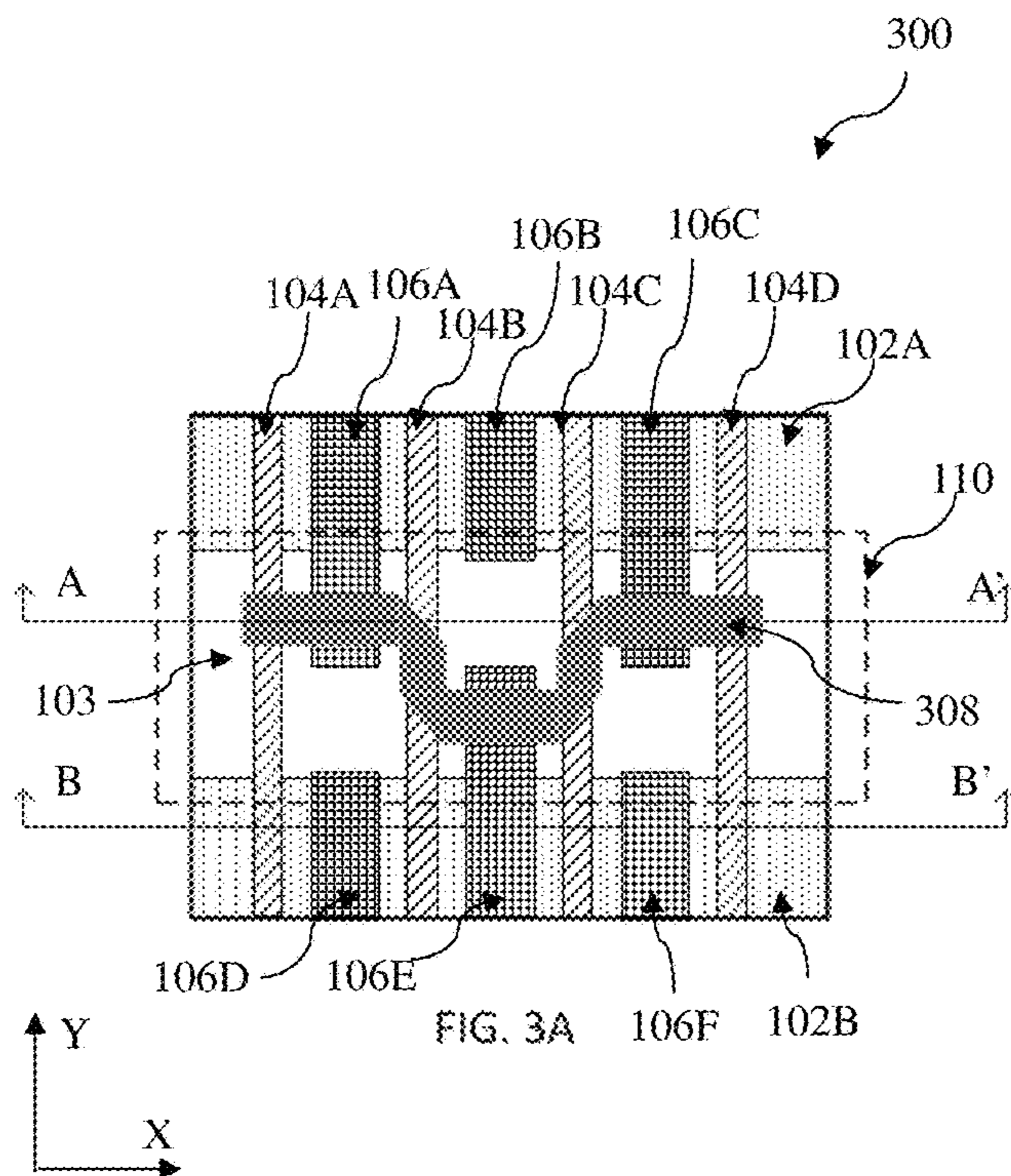
FOREIGN PATENT DOCUMENTS

CN	105895578	A	8/2016
JP	110214898		8/1998
TW	1559509		11/2016

* cited by examiner







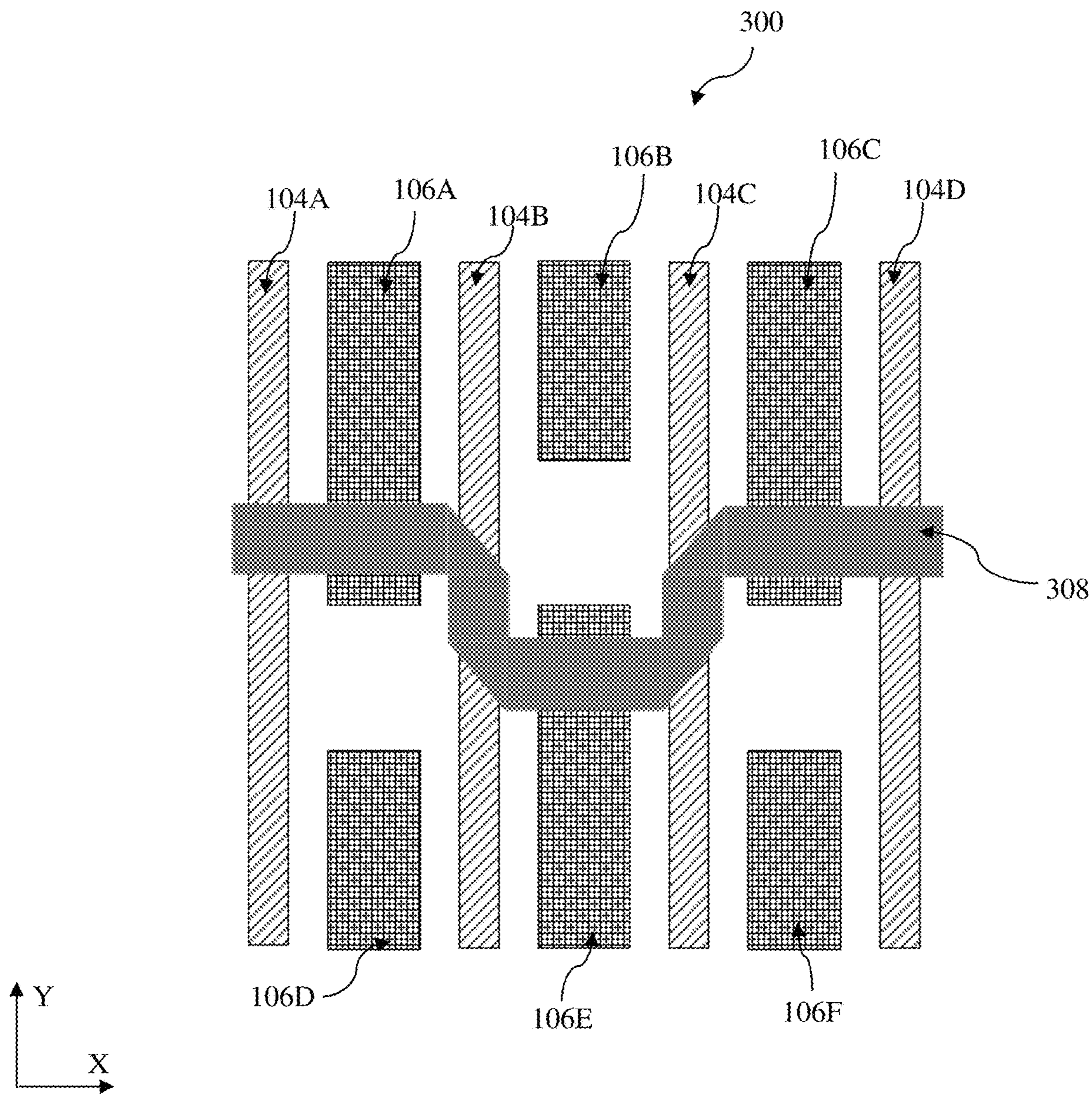


Fig. 4

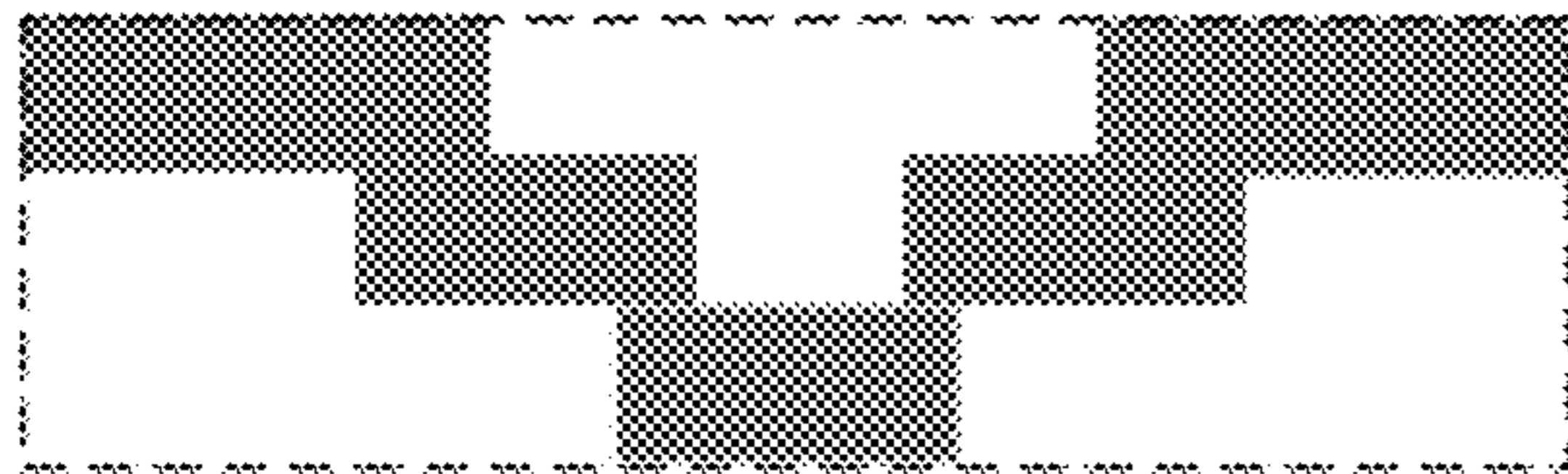


FIG. 5A

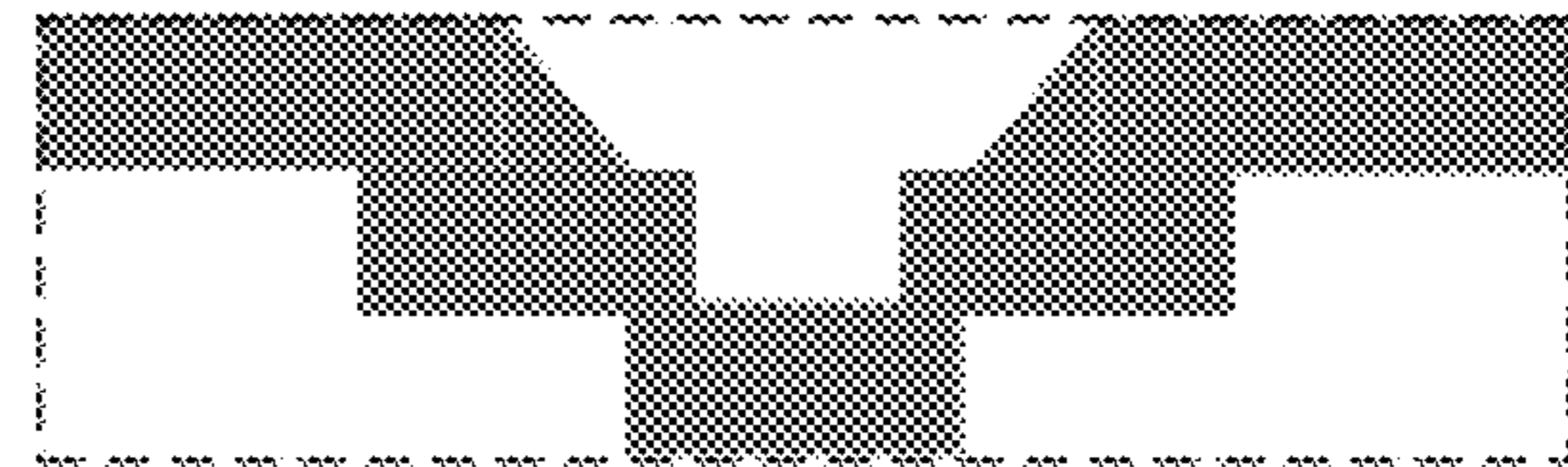


FIG. 5B

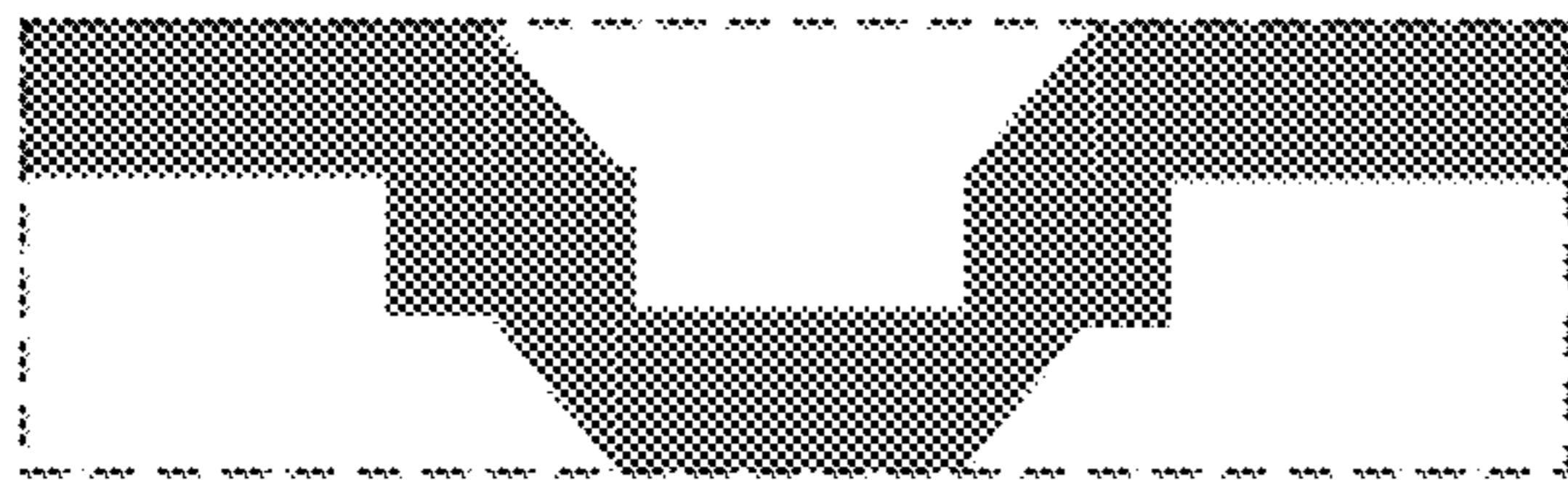


FIG. 5C

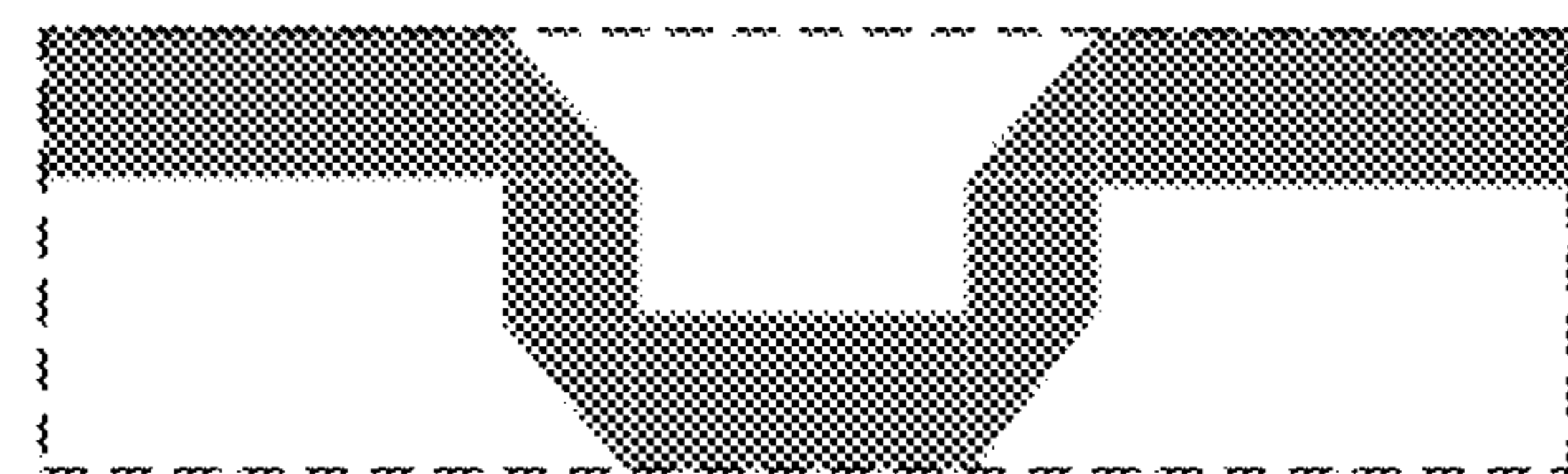


FIG. 5D

308



FIG. 6A

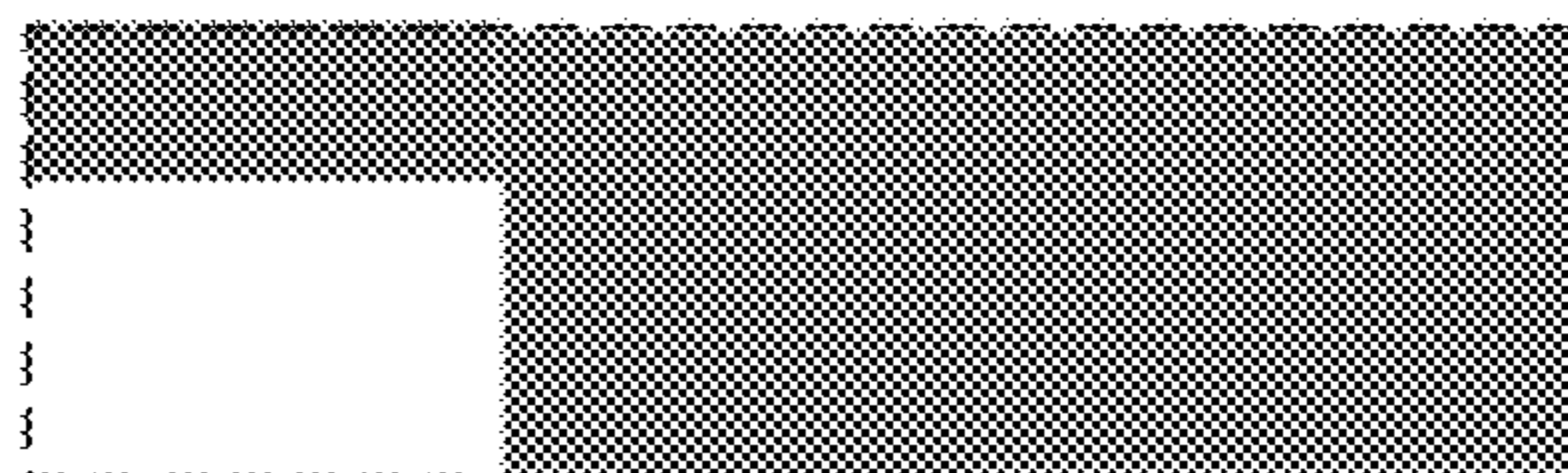


FIG. 6B



FIG. 6C

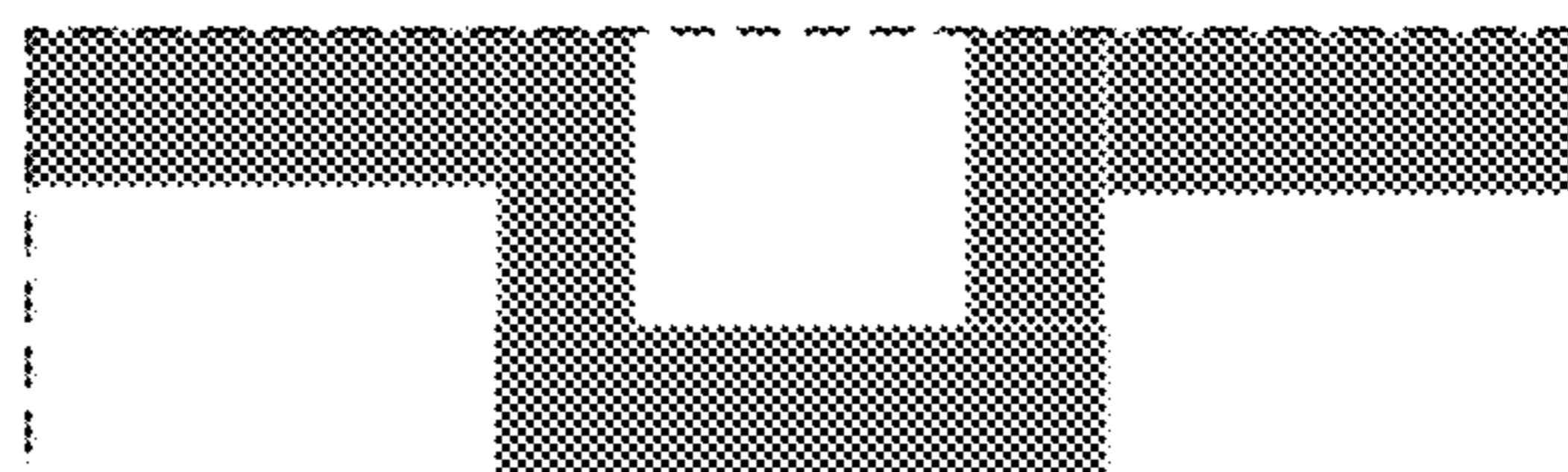


FIG. 6D

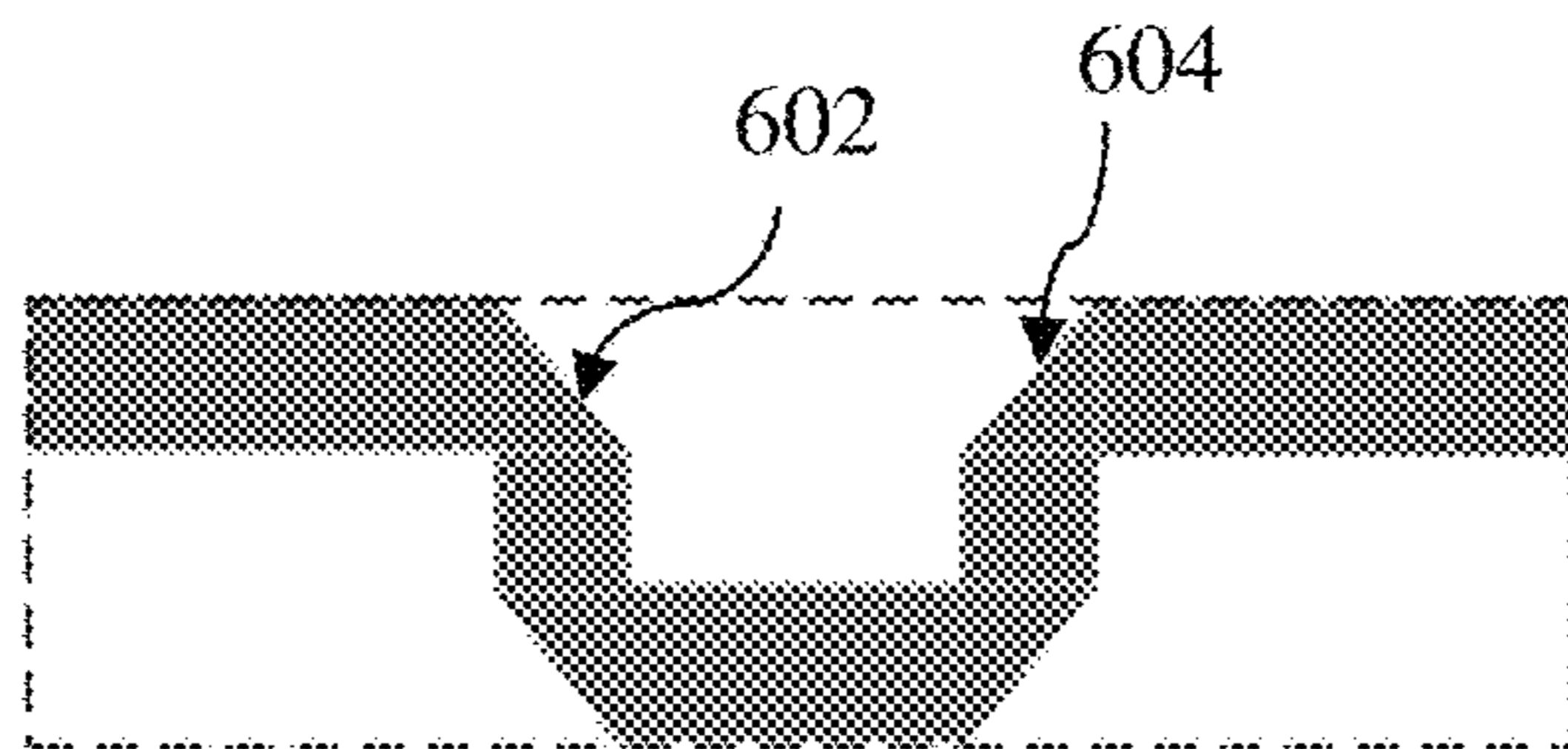
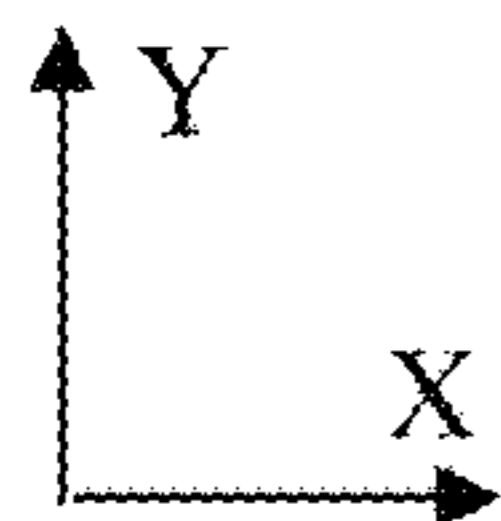


FIG. 6E



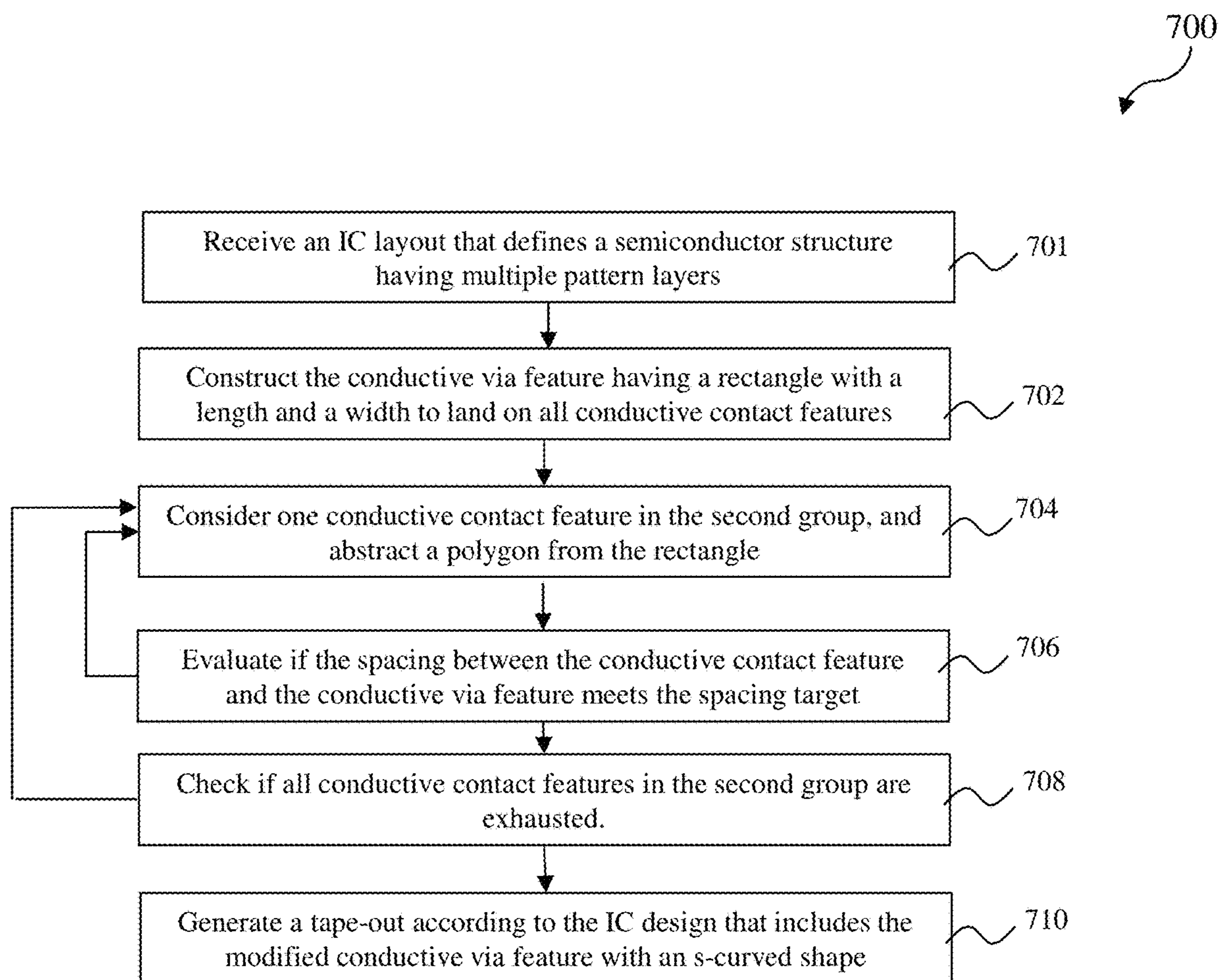


Fig. 7

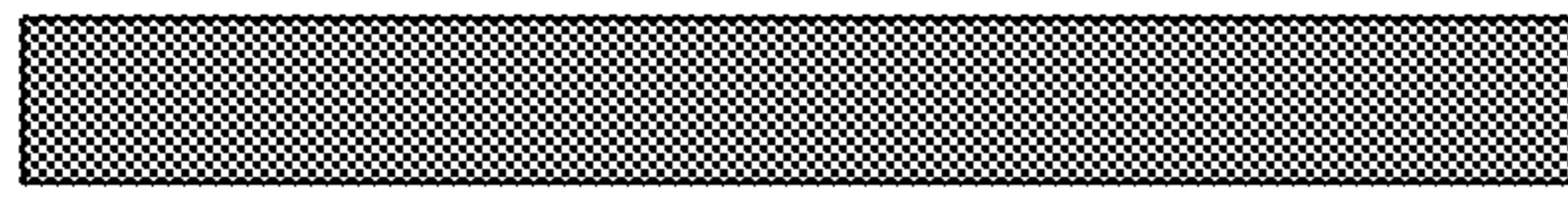


Fig. 8A

308
↙



Fig. 8B

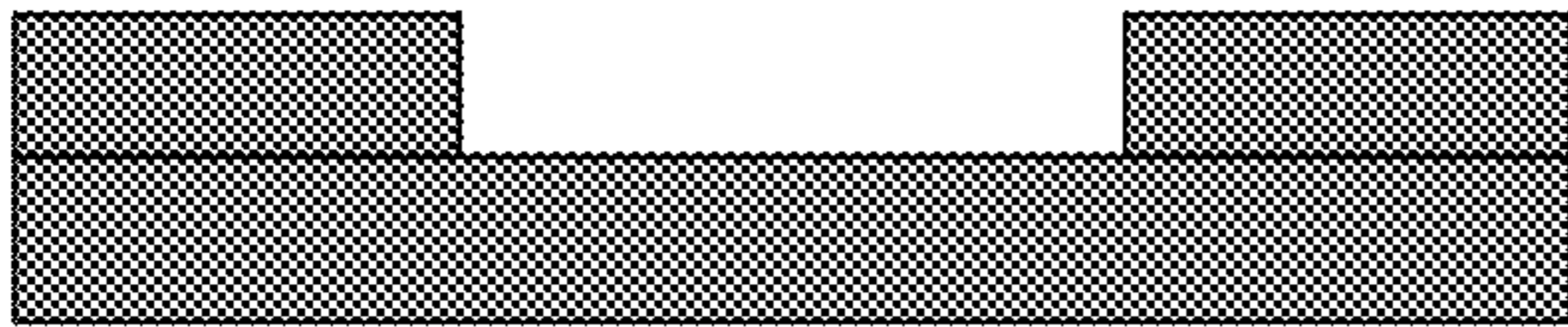


Fig. 8C

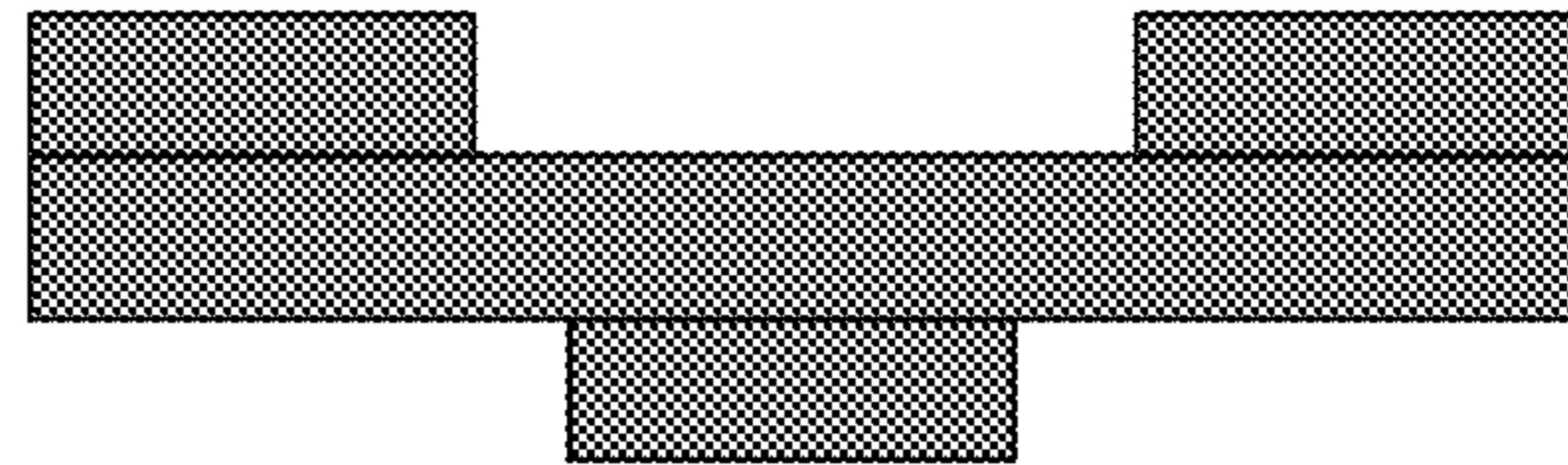


Fig. 8D

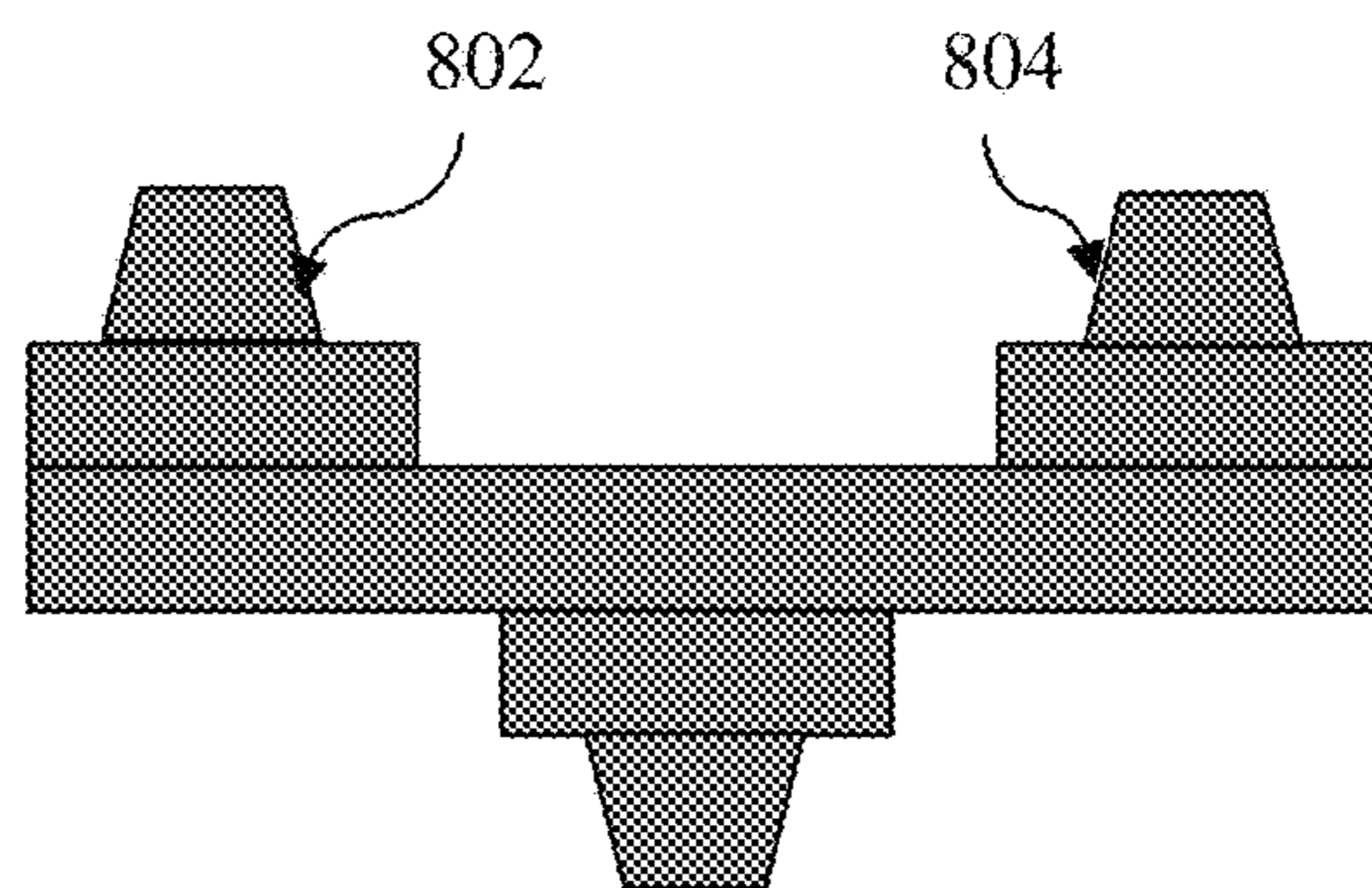
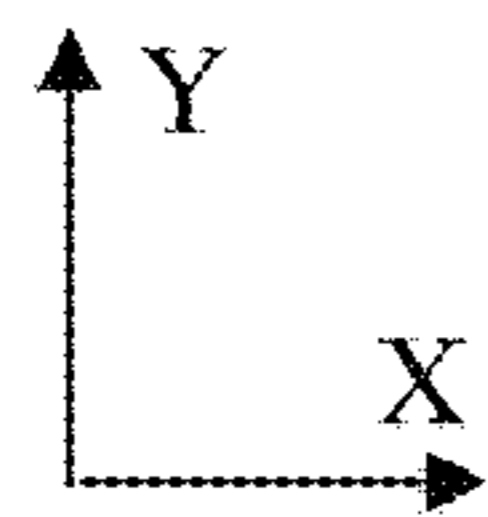


Fig. 8E

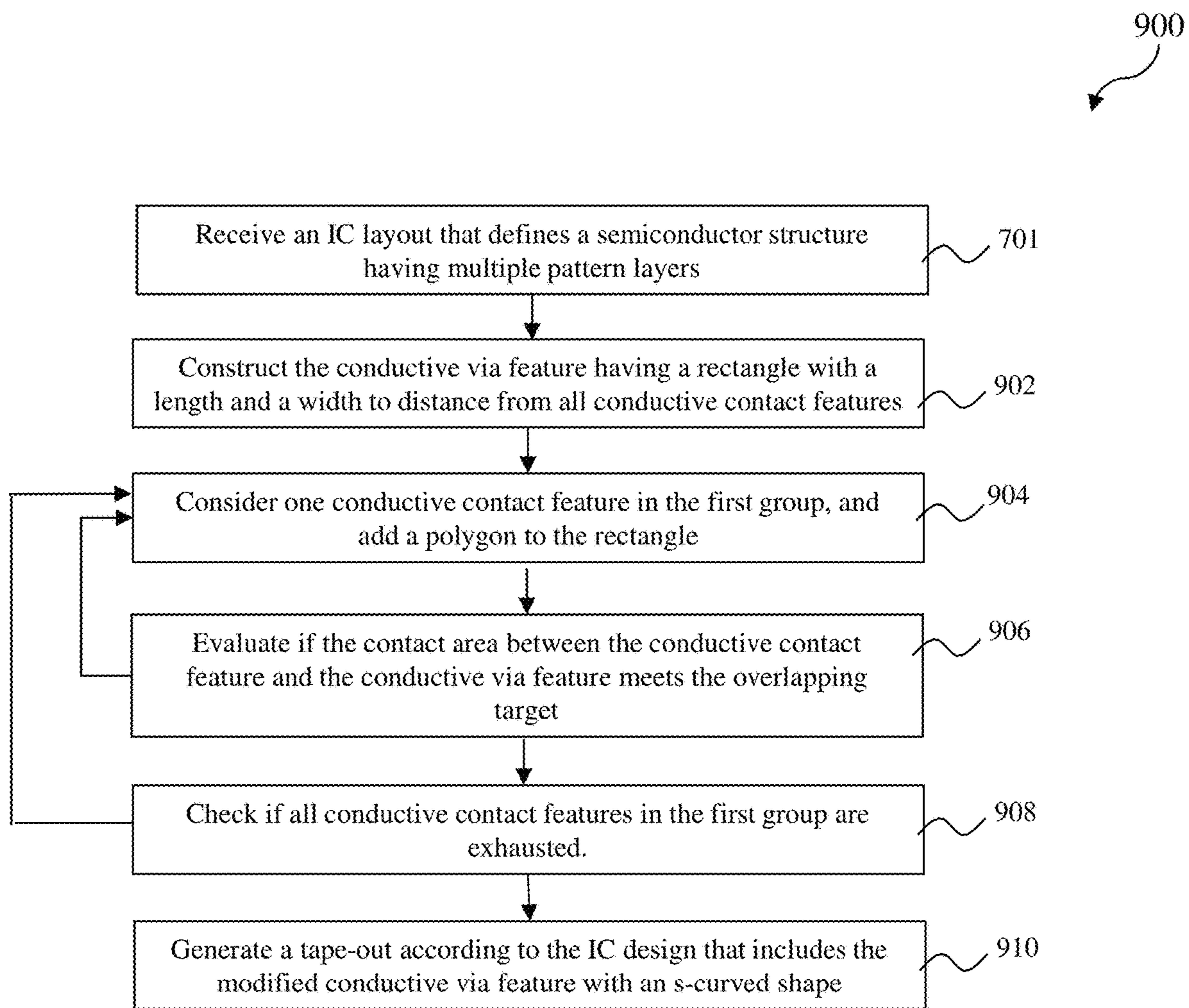


Fig. 9

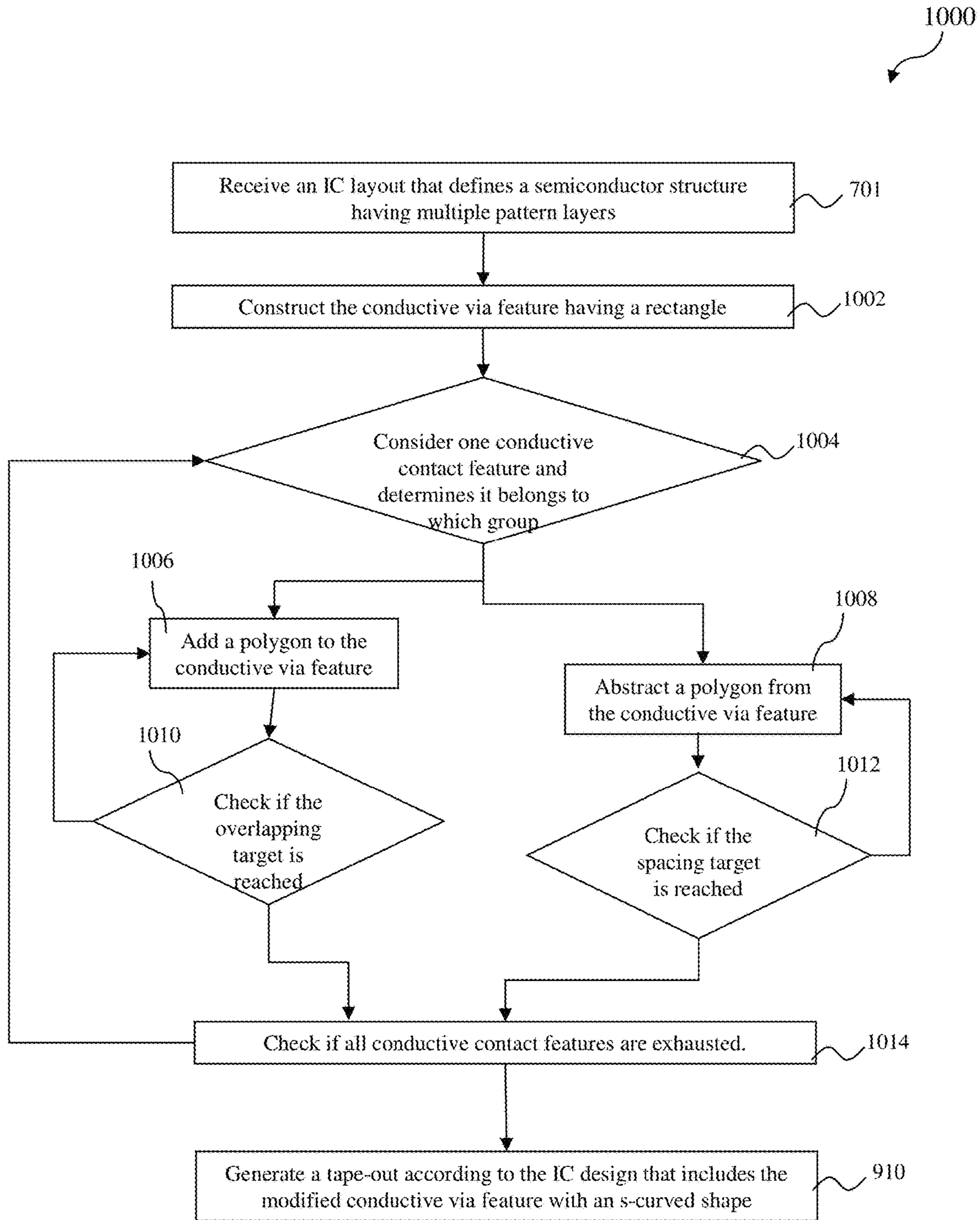


Fig. 10

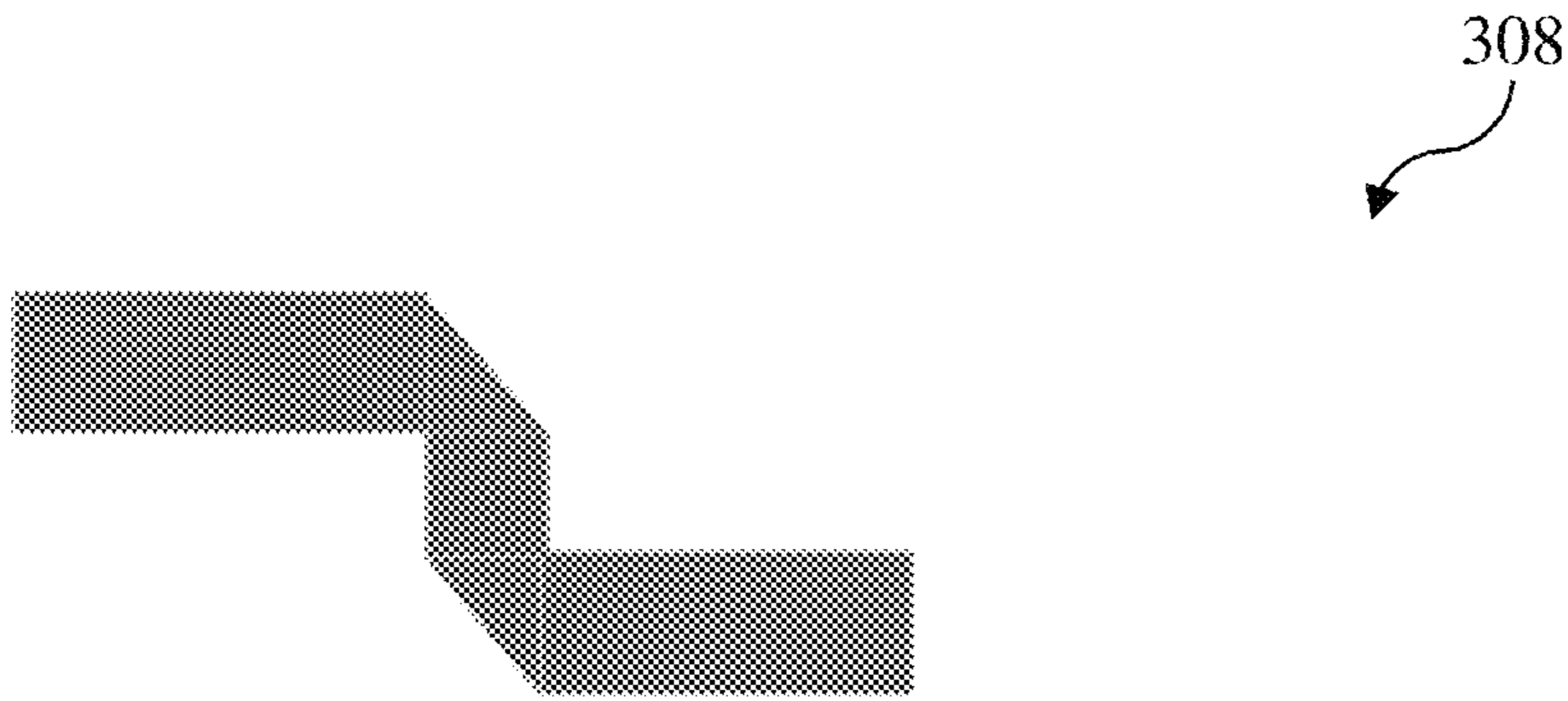


Fig. 11A



Fig. 11B

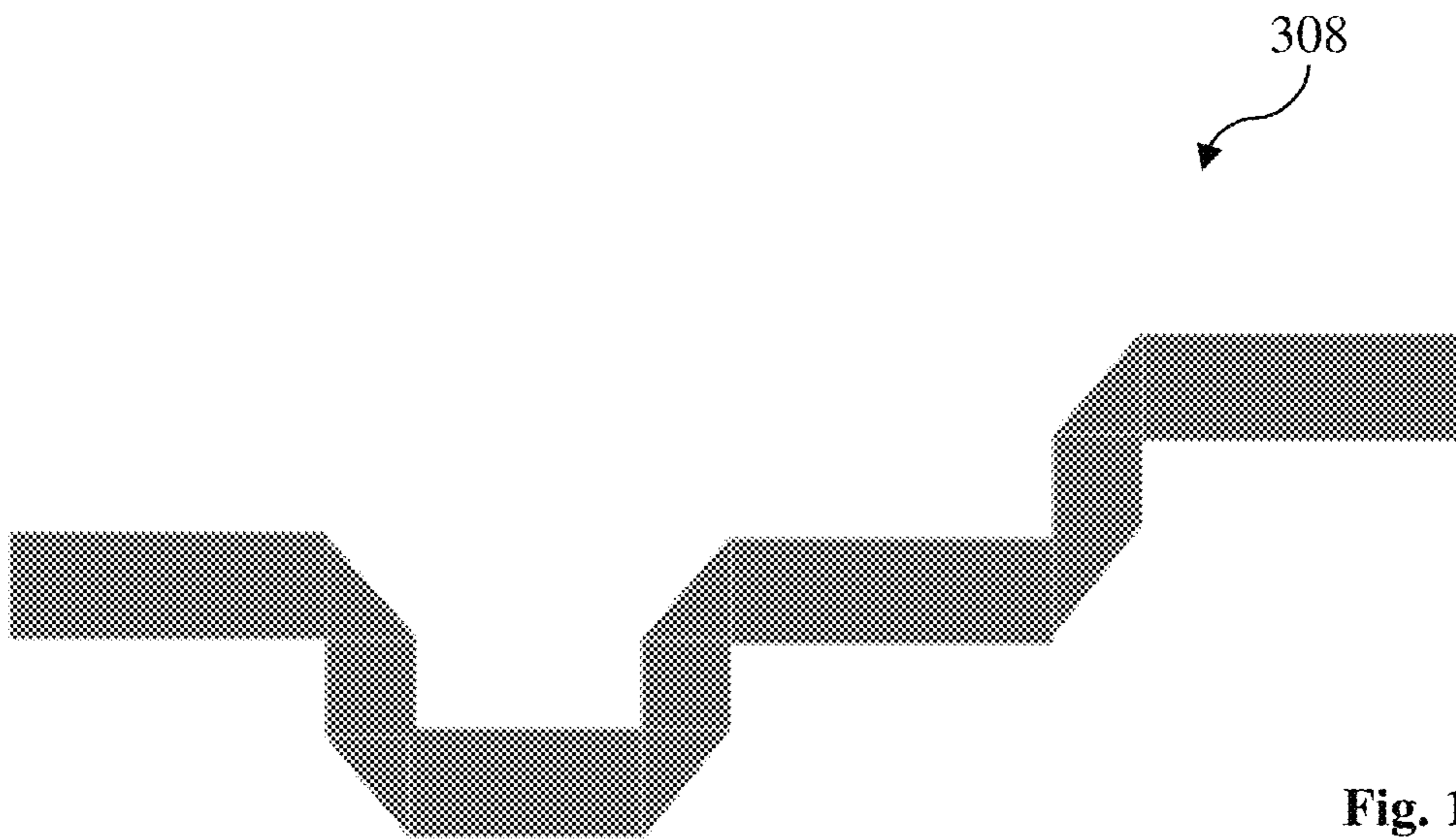


Fig. 11C

1

METHOD AND IC DESIGN WITH
NON-LINEAR POWER RAILS

PRIORITY DATA

This is a continuation application of U.S. patent application Ser. No. 17/106,639, filed Nov. 30, 2020, which is a continuation application of U.S. patent application Ser. No. 16/725,013, filed Dec. 23, 2019, which is a divisional application of U.S. patent application Ser. No. 15/686,336, filed Aug. 25, 2017, each of which is herein incorporated by reference in its entirety.

BACKGROUND

The semiconductor integrated circuit (IC) industry has experienced exponential growth. Technological advances in IC materials and design have produced generations of ICs where each generation has smaller and more complex circuits than the previous generation. In the course of IC evolution, functional density (i.e., the number of interconnected devices per chip area) has generally increased while geometry size (i.e., the smallest component (or line) that can be created using a fabrication process) has decreased.

ICs may include a plurality of standard cell circuits each formed by various logic components, such as transistors, capacitors, or the like, to provide a Boolean logic function or a storage function. Interconnect structures, such as vias and power rails, are then formed over the plurality of standard cell circuits to provide connections between the standard cell circuits and/or to provide connections to external devices. However, as the size of standard cells progressively become smaller, gaps and clearance between the power rails and the other electronic components may decrease which may increase the risk of shorting. Attempts to reduce the size of the power rails, however, may suffer from increased resistance and may induce speed degradation. Accordingly, what is needed is a circuit structure and a method of making the same to address the above issues.

BRIEF DESCRIPTION OF THE DRAWINGS

Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIG. 1A is a top view of a semiconductor structure in accordance with some embodiments.

FIGS. 1B and 1C are sectional views of the semiconductor structure of FIG. 1A, along AA' and BB' dashed lines, respectively, in accordance with some embodiments.

FIG. 2A is a top view of a semiconductor structure in accordance with some embodiments.

FIGS. 2B and 2C are sectional views of the semiconductor structure of FIG. 2A, along AA' and BB' dashed lines, respectively, in accordance with some embodiments.

FIG. 3A is a top view of a semiconductor structure in accordance with some embodiments.

FIGS. 3B and 3C are sectional views of the semiconductor structure of FIG. 3A, along AA' and BB' dashed lines, respectively, in accordance with some embodiments.

FIG. 4 is a top view of the semiconductor structure of FIG. 3A, in portion, constructed according to some embodiments.

2

FIGS. 5A, 5B, 5C and 5D are sectional views of a conductive via feature in the semiconductor structure of FIG. 4 in accordance with some embodiments.

FIGS. 6A, 6B, 6C, 6D and 6E are sectional views of the conductive via feature in the semiconductor structure of FIG. 4 at various fabrication stages, constructed in accordance with some embodiments.

FIG. 7 is a flowchart of an integrated circuit fabrication method in accordance with some embodiments.

FIGS. 8A, 8B, 8C, 8D and 8E are sectional views of the conductive via feature in the semiconductor structure of FIG. 4 at various fabrication stages, constructed in accordance with some embodiments.

FIG. 9 is a flowchart of an integrated circuit fabrication method in accordance with some embodiments.

FIG. 10 is a flowchart of an integrated circuit fabrication method in accordance with some other embodiments.

FIGS. 11A, 11B and 11C are sectional views of the conductive via feature in the semiconductor structure of FIG. 4 at various fabrication stages, constructed in accordance with some embodiments.

DETAILED DESCRIPTION

The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as being “below” or “beneath” other elements or features would then be oriented “above” the other elements or features. Thus, the exemplary term “below” can encompass both an orientation of above and below. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

The present disclosure is directed to, but not otherwise limited to, a field-effect transistor (FET) device. The FET device, for example, may be a complementary metal-oxide-semiconductor (CMOS) device including a P-type metal-oxide-semiconductor (PMOS) FET device and an N-type metal-oxide-semiconductor (NMOS) FET device. The FET may be two-dimensional (planar FET) or three-dimensional, such as a fin-type FET (FinFET). The following disclosure will continue with a FinFET example to illustrate various embodiments of the present invention. It is understood,

however, that the application should not be limited to a particular type of device, except as specifically claimed.

FIG. 1A is a top view of a semiconductor structure **100**; and FIGS. 1B and 1C are sectional views of the semiconductor structure **100** along AA' and BB' directions, respectively, constructed in accordance with some embodiments. The semiconductor structure **100** includes a semiconductor substrate having various active regions (such as **102A** and **102B**) separated by isolation features **103**. Various devices, such as FETs are formed on the active regions. Each of the active regions includes an elongated shape, such as rectangle, oriented in a first direction (X direction). Various gate stacks, such as gate stacks **104A**, **104B** **104C** and **104D**, for FETs are formed on the active regions. Each of the gate stacks includes an elongated shape, such as rectangle, oriented in a second direction (Y direction) that is perpendicular to the first direction. The vertical direction is Z direction, which is perpendicular to the surface of the semiconductor substrate, defined by XY plane. Various source/drain features (not shown) are formed on the fin active regions and are configured with respective gate stacks to form FETs. The semiconductor structure **100** further includes conductive features (also referred to as conductive contact features) **106** formed on the semiconductor substrate and configured to land on the source/drain features. In the present example, the conductive contact features **106** include exemplary conductive contact features **106A**, **106B**, **106C**, **106D**, **106E** and **106F**. In furtherance of the present example, the conductive contact features **106A**, **106B** and **106C** land on and directly contact respective source/drain features on the active region **102A**, while the conductive contact features **106D**, **106E** and **106F** land on and directly contact respective source/drain features on the active region **102B**. A conductive feature (referred to as conductive via feature) **108** is disposed on the semiconductor substrate and is configured to directly connect to the conductive contact features **106A**, **106C** and **106E**. The conductive via feature **108** is a power rail configured to provide power (such as a high power Vdd or a low power Vss) to source/drain features in the semiconductor substrate. Additional interconnection structure, including various metal lines and via features, is formed on the semiconductor substrate and is configured to couple various FETs into a functional circuit. Particularly, the interconnection structure includes a metal line **110** configured to land on the conductive via feature **108**, as illustrated in FIG. 1B.

FIG. 2A is a top view of a semiconductor structure **200**; and FIGS. 2B and 2C are sectional views of the semiconductor structure **100** along AA' and BB' directions, respectively, constructed in accordance with some embodiments. The semiconductor structure **200** includes a semiconductor substrate having various active regions (such as **102A** and **102B**) separated by isolation features **103**. Various devices, such as FETs are formed on the active regions. Each of the active regions includes an elongated shape, such as rectangle, oriented in a first direction (X direction). Various gate stacks, such as gate stacks **104A**, **104B** **104C** and **104D**, for FETs are formed on the active regions. Each of the gate stacks includes an elongated shape, such as rectangle, oriented in a second direction (Y direction) that is perpendicular to the first direction. The vertical direction is Z direction, which is perpendicular to the surface of the semiconductor substrate, defined by XY plane. Various source/drain features (not shown) are formed on the fin active regions and are configured with respective gate stacks to form FETs. The semiconductor structure **200** further includes conductive contact features **106** formed on the semiconductor substrate

and configured to land on the source/drain features. In the present example, the conductive contact features **106** include exemplary conductive contact features **106A**, **106B**, **106C**, **106D**, **106E** and **106F**. In furtherance of the present example, the conductive contact features **106A**, **106B** and **106C** land on and directly contact respective source/drain features on the active region **102A**, while the conductive contact features **106D**, **106E** and **106F** land on and directly contact respective source/drain features on the active region **102B**. Three exemplary conductive via features **208A**, **208B** and **208C** are formed on the semiconductor substrate and are configured to connect to the conductive contact features **106A**, **106E** and **106C**, respectively. The conductive via features **208** are power rails configured to provide power (such as a high power Vdd or a low power Vss) to source/drain features in the semiconductor substrate. Additional interconnection structure, including various metal lines and via features, is formed on the semiconductor substrate and is configured to couple various FETs into a functional circuit. Particularly, the interconnection structure includes a metal line **110** configured to land on and electrically connect to the conductive via features **208A**, **208B** and **208C**, as illustrated in FIG. 2B.

FIG. 3A is a top view of a semiconductor structure **300**; and FIGS. 3B and 3C are sectional views of the semiconductor structure **300** along AA' and BB' directions, respectively, constructed in accordance with some embodiments. The semiconductor structure **300** includes a semiconductor substrate having various active regions (such as **102A** and **102B**) separated by isolation features **103**. Various devices, such as FETs are formed on the active regions. Each of the active regions includes an elongated shape, such as rectangle, oriented in a first direction (X direction). Various gate stacks, such as gate stacks **104A**, **104B** **104C** and **104D**, for FETs are formed on the active regions. Each of the gate stacks includes an elongated shape, such as rectangle, oriented in a second direction (Y direction) that is perpendicular to the first direction. The vertical direction is Z direction, which is perpendicular to the surface of the semiconductor substrate, defined by XY plane. Various source/drain features (not shown) are formed on the fin active regions and are configured with respective gate stacks to form FETs. The semiconductor structure **300** further includes conductive contact features **106** formed on the semiconductor substrate and configured to land on the source/drain features. In the present example, the conductive contact features **106** include exemplary conductive contact features **106A**, **106B**, **106C**, **106D**, **106E** and **106F**. In furtherance of the present example, the conductive contact features **106A**, **106B** and **106C** land on and directly contact respective source/drain features on the active region **102A**, while the conductive contact features **106D**, **106E** and **106F** land on and directly contact respective source/drain features on the active region **102B**. A curved conductive via feature **308** is formed on the semiconductor substrate and is configured to connect to the conductive contact features **106A**, **106E** and **106C**, respectively. Particularly, the conductive via feature **308** is designed to have an S-curved shape. The S-curved shape includes at least one edge oriented in a tilted direction, which is different from the first and second directions (X and Y directions). This design with S-curved shape having a tilted edge provides a conductive structure to properly connect to intended conductive contact features with enough contact area (overlapping target) and to distance from unintended conductive contact features with enough clearance (spacing target). The conductive via feature **308** is a power rail configured to provide power (such as a high power Vdd

5

or a low power V_{ss}) to source/drain features in the semiconductor substrate. Additional interconnection structure, including various metal lines and via features, is formed on the semiconductor substrate and is configured to couple various FETs into a functional circuit. Particularly, the interconnection structure includes a metal line **110** configured to land on the conductive via feature **308**, as illustrated in FIG. 3B.

The semiconductor structure **300** is further constructed in portion in FIG. 4 while the active regions **102** and the metal line **110** are eliminated for simplicity. In the present embodiment, the metal contact features **106** are divided to two groups (or two subsets) according to the relationship to the conductive via feature **308**. The first group of the conductive contact features includes conductive contact features **106A**, **106C** and **106E**, those being intended to be directly connected to the conductive via feature **308** according to the design. The second group of the conductive contact features includes conductive contact features **106B**, **106D** and **106F**, those being intended to be distanced from the conductive via feature **308** according to the design. The S-curved shape of the conductive via feature **308** is a continuous feature with various shifting and deformation to have proper relationships to the two groups of the conductive contact features. The conductive via feature **308** having the S-curved shape is constructed according to various rules, which will be described later, to land on the first group of the conductive contact features satisfying the overlapping target and be distanced from the second group of the conductive contact features satisfying the spacing target. To achieve this, the S-curved shape includes various polygons, such as squares with different sizes, rectangles with different widths and lengths, tilted rectangles with different angles, triangles, trapezoids, diamonds, and parallelograms. Various exemplary S-curved shapes of the conductive via feature **308** are illustrated in FIGS. 5A, 5B, 5C and 5D in accordance with some embodiments. Usually, the original IC design from the designer cannot meet those criteria (such as the overlapping target and spacing target) due to not knowing enough of the manufacturing capability and un-efficiency of the communication between the designers and manufacture. The following method provides a proper way to modify the IC design to meet the manufacturing rules.

FIG. 7 provides a flowchart **700** for constructing the conductive via feature **308** according to some embodiments with the abstract rules. FIGS. 6A, 6B, 6C, 6D and 6E are the shapes of the conductive via feature **308** at various steps. In the following description, the IC design of the semiconductor structure **100** still use the IC design in FIGS. 3A-3C and FIG. 4 for various features (including active regions **102**, gate stacks **104** and other features) and respective spatial relationships.

Referring to FIG. 7, the method **700** begins at a block **701** by receiving an IC layout for a semiconductor structure having multiple pattern layers, such as those illustrated in FIGS. 3A-3C. For examples, the IC layout includes a first pattern layer defining active regions **102**; a second pattern layer defining gate stacks **104**; a third pattern layer defining conductive contact features **106** landing on respective active regions; and a fourth pattern layer defining a conductive via feature **308** landing on a subset (or the first group) of the conductive contact features **106**. Additional pattern layers may be present in the IC layout. For example, an interconnection structure, including various metal lines and via features in respective pattern layers, is formed on the semiconductor substrate and is configured to couple various FETs into a functional circuit.

6

Referring to FIGS. 7 and 6A, the method **700** proceeds to an operation **702** by constructing the conductive via feature having a rectangle with a length and a width to land on all conductive contact features satisfying the overlapping target. In the present example, the rectangle is oriented with its length in the first direction (X direction), as illustrated in FIG. 6A. This rectangle is referred to as an initial rectangle.

Referring to FIGS. 7 and 6B, the method **700** proceeds to an operation **704** by considering one conductive contact feature from the second group, and abstracting a polygon from the initial rectangle. Especially, the abstraction of the polygon is from the location of the overlapping region between the initial rectangle of the conductive via feature and the considered conductive contact feature. The dimensions of the polygon may be evaluated and determined according to certain rules, such as the overlapping area plus the spacing. The polygon can be a polygon with any number of sides, such as a square, a rectangle, a triangle, a trapezoid, a diamonds, and a parallelogram. Edges of the polygon can be in any angle including a tilted angle different from the X and Y directions. For example, the conductive contact feature **106D** is considered and a polygon is abstracted from the overlapping region. In the case, the polygon is a rectangle. After the abstraction at the operation **704**, the shape of the conductive via feature is illustrated in FIG. 6B.

Referring to FIG. 7, the method **700** proceeds to an operation **706** by evaluating if a lateral distance (or spacing) between the considered conductive contact feature (**106D** in this example) and the conductive via feature meets the spacing target. If not, move back to the operation **704** by abstracting another polygon from the conductive via feature. If it meets the spacing target, the method **700** moves forward to the following operation **708**. The method **700** will iterates until the spacing target is reached.

Referring to FIGS. 7, the method **700** proceeds to an operation **708** by check if all conductive contact features in the second group are exhausted. If not, the method **700** moves back to the operation **704** for another conductive contact feature in the second group. For example, consider another conductive contact feature **106F** in the second group and abstract another polygon (such as a rectangle) from the conductive via feature, resulting in a curved shape as illustrated in FIG. 6C. For another example, consider yet another conductive contact feature **106B** in the second group and abstract another polygon (such as a rectangle) from the conductive via feature, resulting in an S-curved shape as illustrated in FIG. 6D. Furthermore, if the spacing target is still not reached yet, another polygon is abstracted from the conductive via feature **308**. For examples, if the conductive contact feature **106D** and the conductive via feature **308** have not enough spacing, another polygon (such as a triangle) is abstracted. For another example, if the conductive contact feature **106F** and the conductive via feature **308** have not enough spacing, another polygon, such as a triangle, is abstracted, and so on, resulting in conductive via feature **308** having an S-curved shape as illustrated in FIG. 6E. Particularly, the S-curved shape **308** in FIG. 6E has one or more tilted edges, such as edges **602**, **604** and other tilted edges, each having a respective tilted angle different from the X and Y directions.

Referring to FIG. 7, the method **700** may include other operations, such as an operation **710** to generate a tape-out for mask making according to thus modified IC design, which includes the conductive via feature **308** having an S-curved shape, which further has at least one tilted edge. The tape-out defines the modified IC design to be formed on photomasks for wafer fabrication or to be directly trans-

ferred to semiconductor wafers by direct writing techniques, such as electron-beam direct writing. The tape-out of the modified IC design includes various pattern layers (such as a layer of active regions, a layer of gate stacks and so on) and spatial relationships among those pattern layers, especially various shapes and sizes of various pattern features in each pattern layer. The method 700 may further include making photomasks according to the tape-out that defines the modified IC design having a conductive via feature 308 with an S-curved shape.

FIG. 9 provides a flowchart 900 for constructing the conductive via feature 308 according to some embodiments with the addition rules. FIGS. 8A, 8B, 8C, 8D and 8E are the shapes of the conductive via feature 308 at various steps. In the following description, the IC design of the semiconductor structure 100 is still use the IC design in FIGS. 3A-3C and FIG. 4 for various features (including active regions 102, gate stacks 104 and other features) and respective spatial relationships.

Referring to FIG. 9, the method 900 begins at a block 701 by receiving an IC layout for a semiconductor structure having multiple pattern layers. For examples, the IC layout includes a first pattern layer defining active regions 102; a second pattern layer defining gate stacks 104; a third pattern layer defining conductive contact features landing on respective active regions; and a fourth pattern layer defining a conductive via feature landing on a subset of the conductive contact features, such as those illustrated in FIGS. 3A-3C. Additional pattern layers may present in the IC layout.

Referring to FIGS. 9 and 8A, the method 900 proceeds to an operation 902 by constructing the conductive via feature having a rectangle with a length and a width small enough so that not landing on any of the conductive contact features or distancing from any of the conductive contact features with a lateral distance satisfying the spacing target, which means that the lateral distance is equal to or greater than the spacing target. In the present example, the rectangle is oriented with its length in the first direction (X direction), as illustrated in FIG. 8A. This rectangle is referred to as an initial rectangle.

Referring to FIGS. 9 and 8B, the method 900 proceeds to an operation 904 by considering one conductive contact feature from the first group, and adding a polygon to the initial rectangle. Especially, the addition of the polygon is to the location of the considered conductive contact feature such that the modified conductive via feature will overlap with the considered conductive contact feature. The dimensions of the polygon may be evaluated and determined according to certain rules, such as the existing spacing plus the overlapping target. The polygon can be a polygon with any number of sides, such as a square, a rectangle, a triangle, a trapezoid, a diamonds, and a parallelogram. Edges of the polygon can be in any angle including a tilted angle different from the X and Y directions. For example, the conductive contact feature 106A is considered and a polygon is added to the conductive via feature. In the case, the polygon is a rectangle. After the addition at the operation 904, the shape of the conductive via feature is illustrated in FIG. 8B

Referring to FIG. 9, the method 900 proceeds to an operation 906 by evaluating if the overlapping area between the considered conductive contact feature (106A in this example) and the conductive via feature meets the overlapping target. If not, move back to the operation 904 by adding another polygon to the conductive via feature. If it meets the overlapping target, the method 900 moves forward to the following operation 908 to check if all conductive contact

features in the first group are exhausted. The method 900 will iterates until the overlapping target is reached.

Referring to FIG. 9, the method 900 proceeds to an operation 908 by check if all conductive contact features in the first group are exhausted by the above operations. If not, the method 900 moves back to the operation 904 for another conductive contact feature in the first group. For example, consider another conductive contact feature 106C in the first group and add another polygon (such as a rectangle) to the conductive via feature, resulting in a curved shape as illustrated in FIG. 8C. For another example, consider another conductive contact feature 106E in the first group and add another polygon (such as a rectangle) to the conductive via feature, resulting in an S-curved shape as illustrated in FIG. 8D. Furthermore, if the overlapping target is not reached yet, another polygon is added to the conductive via feature 308. For examples, if the conductive contact feature 106A and the conductive via feature 308 have not enough contact area, another polygon (such as a trapezoid) is added to the conductive via feature. For another example, if the conductive contact feature 106C and the conductive via feature 308 have not enough contact area, another polygon (such as a trapezoid) is added, and so on, resulting in conductive via feature 308 having an S-curved shape as illustrated in FIG. 8E. Particularly, the S-curved shape 308 in FIG. 8E has one or more tilted edges, such as edges 802, 804 and other tilted edges, each having a respective tilted angle different from the X and Y directions. The tilted angle of the conductive via feature 308 is generated since a tilted polygon is added to increase the contact area and also to avoid violate the spacing target to the adjacent conductive contact features in the second group.

Referring to FIG. 9, the method 900 may include other operations, such as an operation 910 to generate a tape-out for mask making according to thus modified IC design, which includes the conductive via feature having an S-curved shape, which further has at least one tilted edge. The tape-out defines the modified IC design to be formed on photomasks or to be directly transferred to semiconductor wafers by direct writing techniques, such as electron-beam direct writing. The tape-out of the modified IC design includes various pattern layers and spatial relationships among those pattern layers, especially various shapes and sizes of various pattern features in each pattern layer. The method 900 may further include making photomasks according to the tape-out that defines the modified IC design having a conductive via feature with an S-curved shape.

FIG. 10 provides a flowchart 1000 for constructing the conductive via feature 308 in accordance with some embodiments. The method 1000 begins at a block 701 by receiving an IC layout for a semiconductor structure having multiple pattern layers. For examples, the IC layout includes a first pattern layer defining active regions 102; a second pattern layer defining gate stacks 104; a third pattern layer defining conductive contact features landing on respective active regions; and a fourth pattern layer defining a conductive via feature landing on a subset of the conductive contact features, such as those illustrated in FIGS. 3A-3C. Additional pattern layers may present in the IC layout.

The method 1000 proceeds to an operation 1002 by constructing an initial shape of the conductive via feature. The initial shape may be a polygon or other proper shape. The initial shape may be a shape from the designer when the initial IC design is received from the designer. In one embodiment, the operation 1002 constructs the initial shape of the conductive via feature to have a rectangle with a length and a width to land on all conductive contact features

satisfying the overlapping target. In another embodiment, the operation **1002** constructs the initial shape of the conductive via feature to have a rectangle with a length and a width small enough so that not landing on any of the conductive contact features or distancing from each of the conductive contact features with a lateral distance satisfying the spacing target.

The method **1000** proceeds to an operation **1004** by considering one conductive contact feature and determine which group it belongs to. In the operation **1004**, a spatial parameter between the conductive via feature and the considered conductive contact feature is evaluated. This spatial relationship defines if the two are connected or distanced away according to the IC layout. Accordingly, the conductive contact features are divided into two groups. The first group includes all conductive contact features to be contacted with the conductive via feature. The second group includes all conductive contact features to be distanced from the conductive via feature. If the considered conductive contact feature belongs to the first group, proceeds to an operation **1006**. If it belongs to the second group, proceeds to an operation **1008**.

At the operation **1004**, when the considered conductive contact feature is from the first group, the method **1000** proceeds to an operation **1006**. At the operation **1006**, a polygon is added to the conductive via feature. Especially, the addition of the polygon is to the location of the considered conductive contact feature such that the modified conductive via feature will overlap with the considered conductive contact feature. The dimensions of the polygon may be evaluated and determined according to certain rules, such as the existing spacing plus the overlapping target. The polygon can be a polygon with any number of sides, such as a square, a rectangle, a triangle, a trapezoid, a diamond, and a parallelogram. Edges of the polygon can be in any angle including a tilted angle different from the X and Y directions. For example, the conductive contact feature **106A** is considered and a polygon is added to the conductive via feature.

The method **1000** proceeds to an operation **1010** by evaluating if the overlapping area between the considered conductive contact and the conductive via feature meets the overlapping target. If not, move back to the operation **1006** by adding another polygon to the conductive via feature. The method **1000** will iterates until the overlapping target is reached. If it meets the overlapping target, the method **1000** moves forward to the following operation **1014**. In the operations **1006** and **1010**, the spacing rule may be also considered. When adding a polygon causes a lateral distance between the conductive via feature **308** and an adjacent conductive contact feature of the second group is reduced, a tilted polygon may be added to both meet the overlapping target and the spacing target.

At the operation **1004**, when the considered conductive contact feature belongs to the second group, the method **1000** proceeds to an operation **1008**. At the operation **1008**, a polygon is abstracted from the conductive via feature. Especially, the abstraction of the polygon is from the location of the considered conductive contact feature such that the modified conductive via feature will distanced from the considered conductive contact feature such that a lateral distance therebetween is equal to or greater than the spacing target. The dimensions of the polygon may be evaluated and determined according to certain rules, such as the existing overlapping plus the spacing target. The polygon can be a polygon with any number of sides, such as a square, a rectangle, a triangle, a trapezoid, a diamond, and a paral-

lelogram. Edges of the polygon can be in any angle including a tilted angle different from the X and Y directions.

The method **1000** proceeds to an operation **1012** by evaluating if the spacing between the considered conductive contact and the conductive via feature meets the spacing target. If not, move back to the operation **1008** by abstracting another polygon from the conductive via feature. The method **1000** will iterates until the spacing target is reached. If it meets the spacing target, the method **1000** moves forward to the following operation **1014**. In the operations **1008** and **1012**, the overlapping rule may be also considered. When abstracting a polygon causes an overlapping area between the conductive via feature **308** and an adjacent conductive contact feature of the first group is reduced, a tilted polygon may be abstracted to both meet the spacing target and the overlapping target.

The operation **1014** includes checking if all conductive contact features (both in the first group and the second group) are exhausted by the above operations. If not, the method **1000** moves back to the operation **1004** for another conductive contact feature. Thus, the conductive via feature **308** ends up with an S-curved shape having one or more tilted edges each with a respective tilted angle different from the X and Y directions.

The method **1000** may include other operations, such as an operation **910** to generate a tape-out for mask making according to thus modified IC design, which includes a conductive via feature having an S-curved shape, which further has at least one tilted edge. The tape-out defines the modified IC design to be formed on photomasks or to be directly transferred to semiconductor wafers by direct writing techniques, such as electron-beam direct writing. The tape-out of the modified IC design includes various pattern layers and spatial relationships among those pattern layers, especially various shapes and sizes of various pattern features in each pattern layer. The method **900** may further include making photomasks according to the tape-out that defines the modified IC design having a conductive via feature with an S-curved shape. The method **900** may further include making semiconductor wafers using the photomasks.

Various embodiments of an IC design for the semiconductor structure and the method making the same are provided. Other embodiments may present within the scope of the present disclosure. For example, the method **700** may begin with an initial shape, and then adding a polygon to reach another conductive contact feature in the first group in a way (in term of shape, size, and tilted angle) be distanced away from an adjacent conductive contact features in the second group. This procedure is continued until the conductive via feature lands on all conductive contact features in the first group with enough contact area (meeting the overlapping target) and is distanced away from all conductive contact features in the second group with enough spacing (meeting the spacing target). At one step, the exemplary conductive via feature **308** is illustrated in FIG. **11A**. After adding a few more additional polygons, the exemplary conductive via feature **308** is extended, as illustrated in FIG. **11B**. After a few more cycles in the iteration of adding polygon, the exemplary conductive via feature **308** is further extended, as illustrated in FIG. **11C**.

The present disclosure provides an IC layout for a semiconductor structure and a method making the same. The semiconductor structure includes a conductive via feature landing on a subset of conductive contact features in the underlying conductive layer to coupling various source/drain features of FETs in the active regions. The conductive

via feature in the IC layout for the semiconductor structure is designed to have an S-curved shape. The S-curved shape includes at least one edge oriented in a tilted direction, which is different from the standard directions, such as the orientation of the elongate gate stacks and the orientation of the elongated fin active regions.

The embodiments of the present disclosure offer advantages over existing art, though it is understood that other embodiments may offer different advantages, not all advantages are necessarily discussed herein, and that no particular advantage is required for all embodiments. By utilizing the disclosed method and structure, the S-curved shape of the conductive via feature provide freedom and flexibility to land on the intended conductive contact features with enough contact areas and distanced away from the unintended conductive contact features with enough clearance.

Thus, the present disclosure provides a method for fabricating an integrated circuit (IC). The method includes receiving an IC layout having active regions, conductive contact features landing on the active regions, and a conductive via feature to be landing on a first subset of the conductive contact features and to be spaced from a second subset of the conductive contact features; evaluating a spatial parameter of the conductive via feature to the conductive contact features; and modifying the IC layout according to the spatial parameter such that the conductive via feature has a S-curved shape.

The present disclosure provides a method for fabricating an integrated circuit (IC). The method includes receiving an IC layout having a first pattern layer, a second pattern layer, and a third pattern layer to be formed on respective material layers of a semiconductor substrate. The first pattern layer includes a first active region and a second active region both having elongated shapes oriented in a first direction. The second pattern layer includes a plurality of conductive contact features having an elongated shape oriented in a second direction being orthogonal to the first direction, wherein the conductive contact features lands on the first and second active regions. The third pattern layer includes a conductive via feature landing on the conductive contact features. The method further includes constructing an initial shape of the conductive via feature; and modifying the initial shape of the conductive via feature to a modified shape that is overlapped with a first subset of the conductive contact features and is distanced from a second subset of the conductive contact features. The modified shape has a S-curved polygon with an edge oriented in a tilted direction being different from the first and second directions.

The present disclosure provides a method for fabricating an integrated circuit (IC). The method includes receiving an IC layout having a first pattern layer and a second pattern layer to be formed on respective material layers of a semiconductor substrate. The first pattern layer includes first conductive contact features and second conductive contact features spaced along a first direction, each of the first and second contact features having an elongated shape oriented in a second direction orthogonal to the first direction. The second pattern layer includes a conductive via feature to be landing on the first the conductive contact features and to be distanced away from the second conductive contact features. The method further includes modifying the conductive via feature to a first polygon that is overlapped with the first conductive contact features and is distanced from the second conductive contact features. The first polygon has an edge oriented in a tilted direction being different from the first and second directions.

The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A method of fabricating an integrated circuit (IC), comprising:

receiving an IC layout having a first pattern layer that includes first source/drain (S/D) contacts and second S/D contacts, the first and second S/D contacts are spaced away from each other by a spacing along a first direction, and each of the first and second S/D contacts have elongated shapes extending lengthwise in a second direction perpendicular to the first direction;

constructing a conductive feature on a second pattern layer of the IC layout, the conductive feature having an initial rectangular shape with a length and a width, the length extending along the first direction; and modifying the conductive feature to form a modified conductive feature that is overlapped with the first S/D contacts and distanced away from the second S/D contacts.

2. The method of claim 1, wherein the modifying of the conductive feature includes:

abstracting a first polygon from the conductive feature if a lateral distance between one of the second S/D contacts and the conductive feature is less than a spacing target; and

adding a second polygon to the conductive feature if an overlapping area between one of the first S/D contacts and the conductive feature is less than an overlapping target.

3. The method of claim 2, wherein the modifying of the conductive feature further includes:

abstracting additional polygons from the conductive feature until the lateral distance meets the spacing target; and

adding additional polygons to the conductive feature until the overlapping area meets the overlapping target.

4. The method of claim 3, wherein the modifying of the conductive feature further includes:

evaluating a lateral distance between each of the second S/D contacts and the conductive feature; and modifying the conductive feature until each lateral distance meets the spacing target.

5. The method of claim 3, wherein the modifying of the conductive feature further includes:

evaluating an overlapping area between each of the first S/D contacts and the conductive feature; and modifying the conductive feature until each overlapping area meets the overlapping target.

6. The method of claim 1, wherein the initial rectangular shape has a length and width such that the conductive feature lands on both the first and second S/D contacts.

7. The method of claim 6, wherein the modifying of the conductive feature includes abstracting a shape from the conductive feature if a lateral distance between one of the second S/D contacts and the conductive feature is less than

13

a spacing target, wherein each of the shape is a two-dimensional polygon chosen from a square, a rectangle, a triangle, a trapezoid, a diamond, and a parallelogram.

8. The method of claim **7**, wherein the modifying of the conductive feature further includes abstracting additional shapes from the conductive feature until all lateral distance between the second S/D contacts and the conductive feature meets the spacing target.

9. The method of claim **1**, wherein the initial rectangular shape has a length and width such that the conductive feature is not landing on any of the first and second S/D contacts.

10. The method of claim **9**, wherein the modifying of the conductive feature includes adding a shape to the conductive feature if an overlapping area between one of the first S/D contacts and the conductive feature is less than an overlapping target, wherein each of the shape is a two-dimensional polygon chosen from a square, a rectangle, a triangle, a trapezoid, a diamond, and a parallelogram.

11. The method of claim **10**, wherein the modifying of the conductive feature further includes adding additional shapes to the conductive feature until all overlapping areas between the first S/D contacts and the conductive feature meets the overlapping target.

12. The method of claim **1**, further comprising:

generating a tape-out of the IC layout; and

forming a semiconductor structure over a substrate according to the tape-out, wherein the forming of the semiconductor structure includes forming the modified conductive feature and forming the first and second S/D contacts,

wherein the modified conductive feature directly lands on the first S/D contacts without landing on the second S/D contacts.

13. A method for fabricating an integrated circuit (IC), comprising:

receiving an IC layout having a first pattern layer and a second pattern layer to be formed on respective material layers of a semiconductor substrate, wherein the first pattern layer includes first S/D contacts and second S/D contacts, the first and second S/D contacts spaced away from each other along a first direction and along a second direction perpendicular to the first direction, and

the second pattern layer includes a conductive feature to be landing on the first S/D contacts and to be distanced away from the second S/D contacts; and

modifying the conductive feature to form a modified conductive feature that is overlapped with the first S/D contacts and distanced away from the second S/D contacts, wherein the modified conductive feature has

14

a shape with tilted edges at a tilted direction different from the first and second directions.

14. The method of claim **13**, wherein the modified conductive feature is a continuous polygon having an S-curved shape.

15. The method of claim **13**, wherein the modifying of the conductive feature includes:

abstracting a first polygon from the conductive feature until a lateral distance between one of the second S/D contacts and the conductive feature meets a spacing target; or

adding a second polygon to the conductive feature until an overlapping area between one of the first S/D contacts and the conductive feature meets an overlapping target.

16. A semiconductor structure, comprising:

first and second active regions extending lengthwise along a first direction over a substrate;

an isolation feature over the substrate and separating the first and second active regions;

first source/drain (S/D) features over first S/D regions of the first and second active regions;

second S/D features over second S/D regions of the first and second active regions;

first and second S/D contacts directly landing on the first and second S/D features, respectively; and

a conductive via feature directly landing on the first S/D contacts without landing on the second S/D contacts, wherein the conductive via feature has a continuous shape, and the conductive via feature includes tilted edges, the tilted edges extending in a direction different from the first direction and different from a second direction perpendicular to the first direction.

17. The semiconductor structure of claim **16**,

wherein the first and second S/D contacts have extending portions that extend directly above the isolation feature along the second direction,

wherein a first length of each of the extending portions of the first S/D contacts is greater than a second length of each of the extending portions of the second S/D contacts.

18. The semiconductor structure of claim **16**, wherein the conductive via feature has an S-curved shape.

19. The semiconductor structure of claim **18**, wherein the S-curved shape includes various polygons such as squares, triangles, trapezoids, diamonds, or parallelograms.

20. The semiconductor structure of claim **16**, further comprising a metal line directly landing on the conductive via feature.

* * * * *